

# PHOTON DETECTION: Scintillators, PMTs and SiPMs

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4<sup>th</sup> June 2019

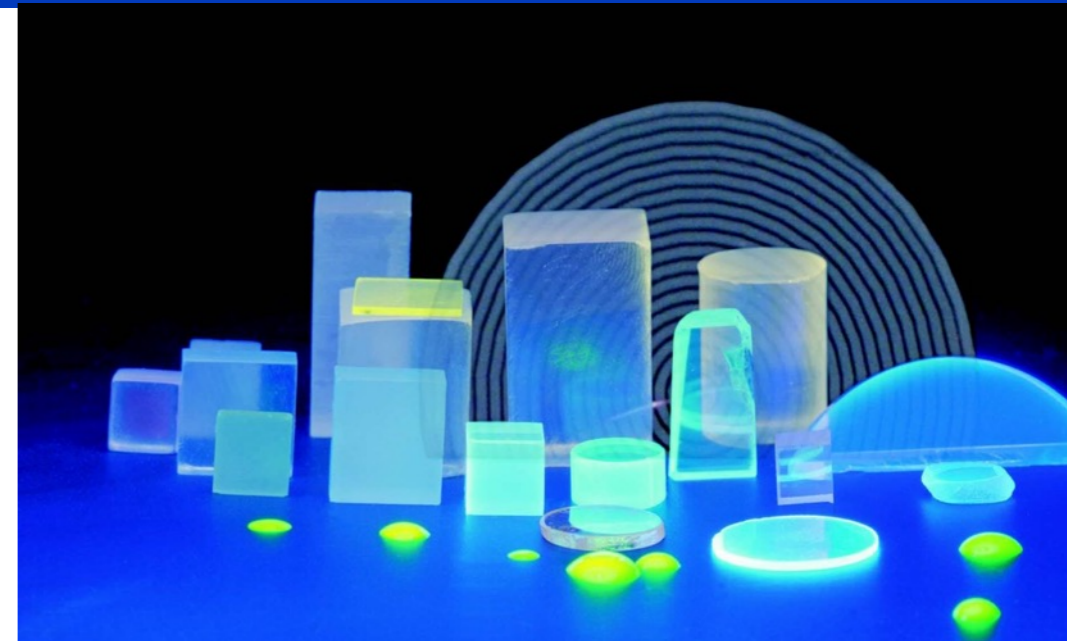
New Directions in the Search  
for Light Dark Matter Particles



# Overview

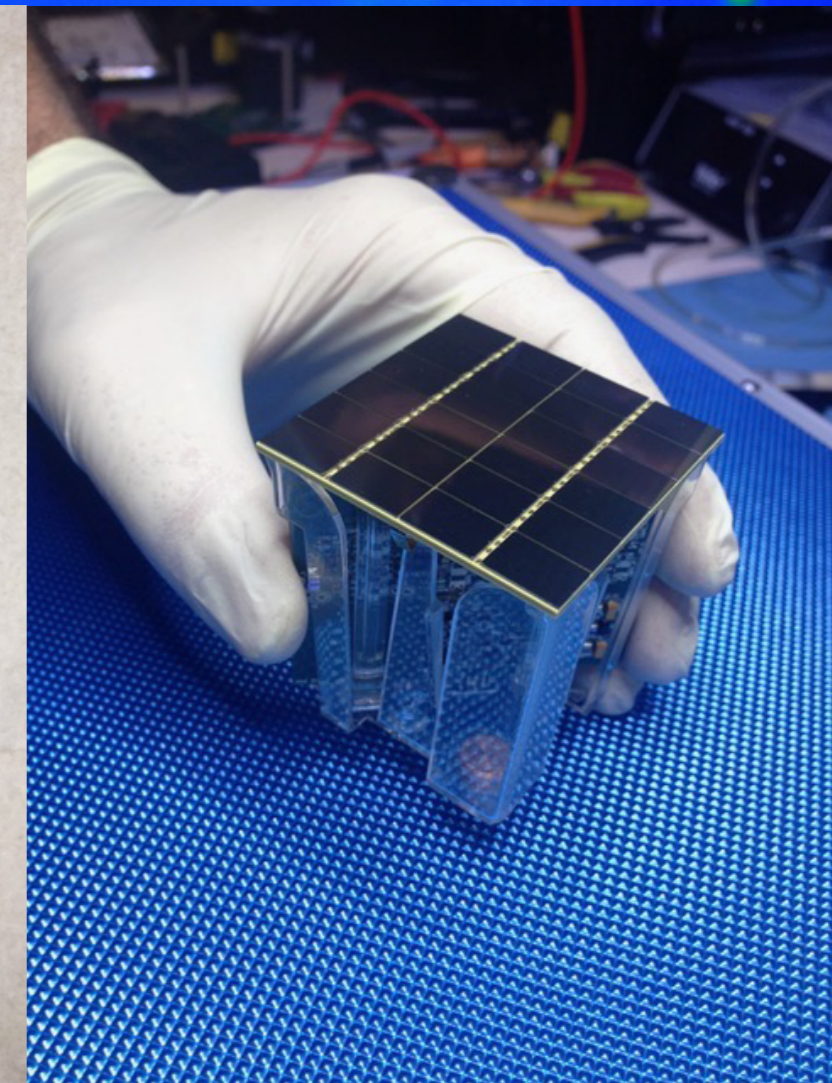
## Scintillation in dark matter search

- Mechanisms
- Properties
- Wavelength shifters
- Ultra-pure scintillators



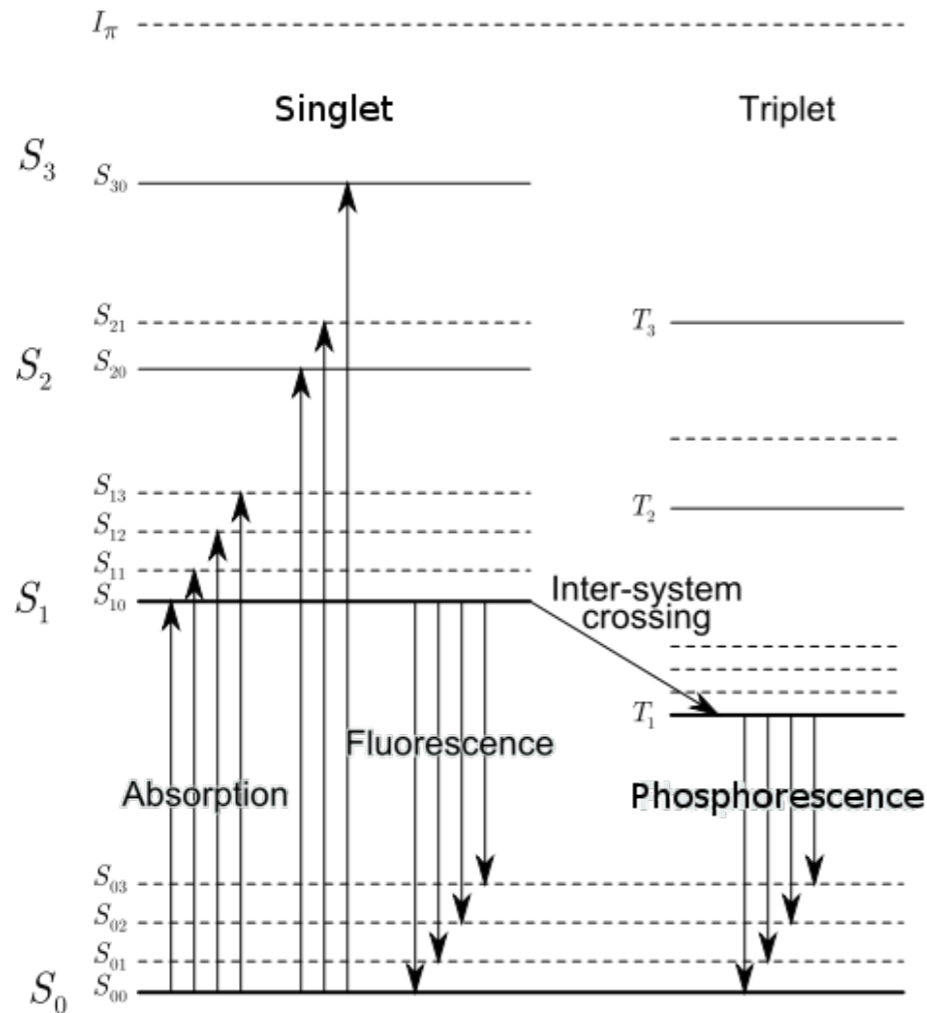
## Single photon detectors

- Operation of PMTs and SiPMs
- Signal features
- Noises
- Operation in cryogenics
- Comparison
- SiPMs tiling and readout

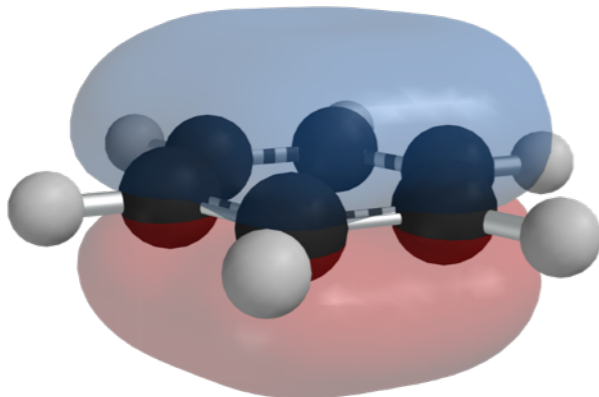


# Scintillation mechanisms

## Organic scintillators

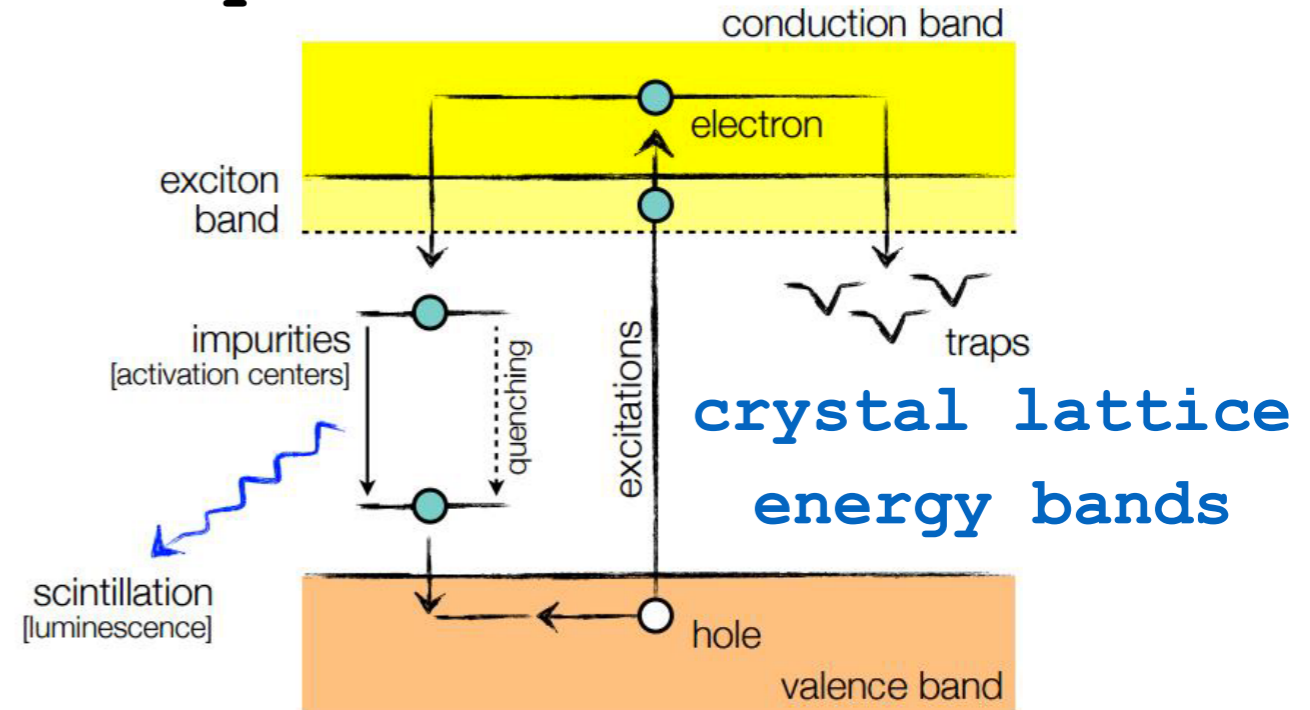


$\pi$ -orbitals in molecules

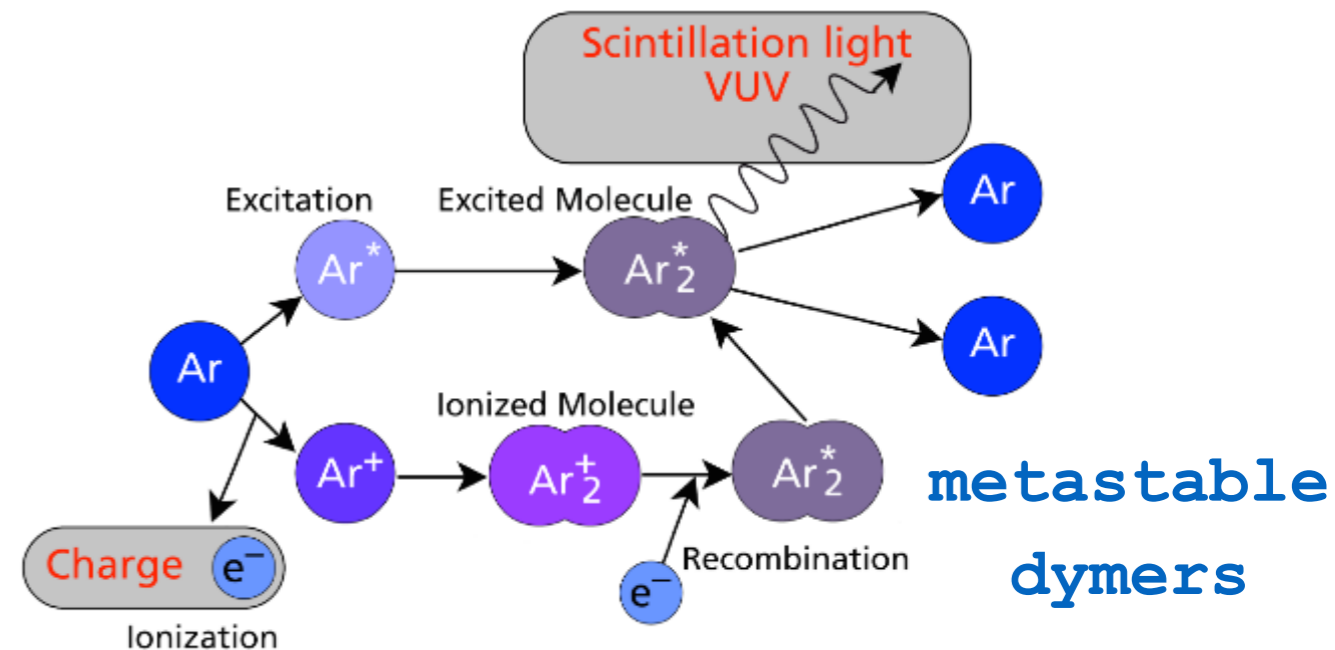


## Inorganic scintillators

### Crystals with Activators



### Noble liquids

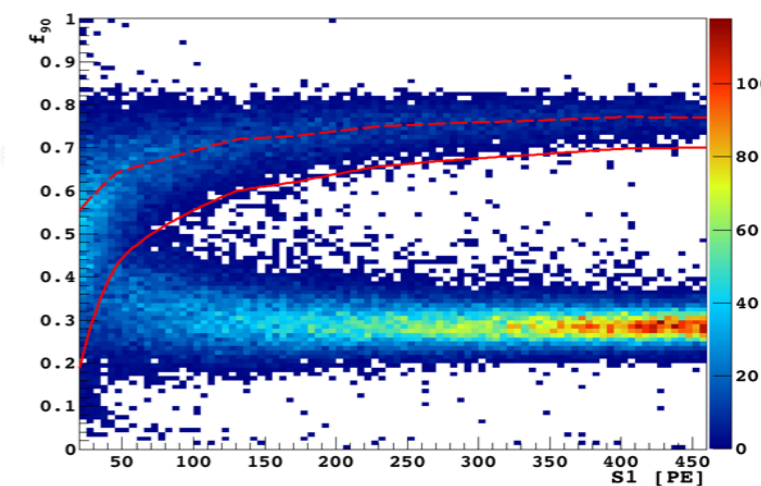
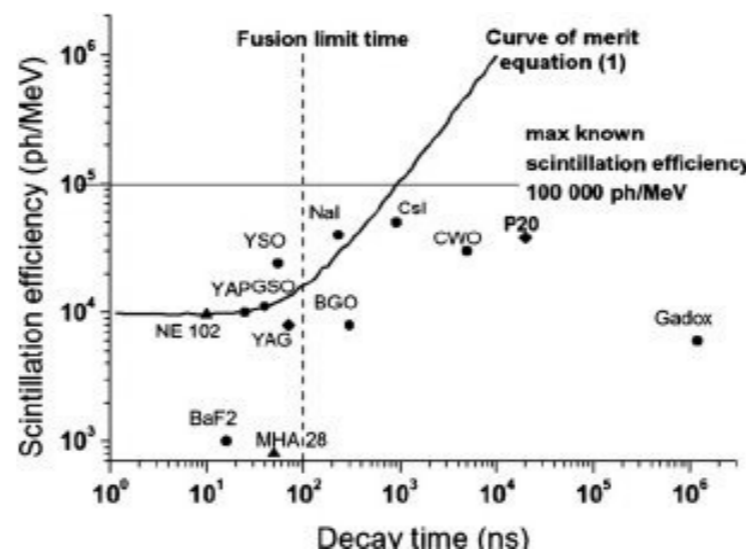
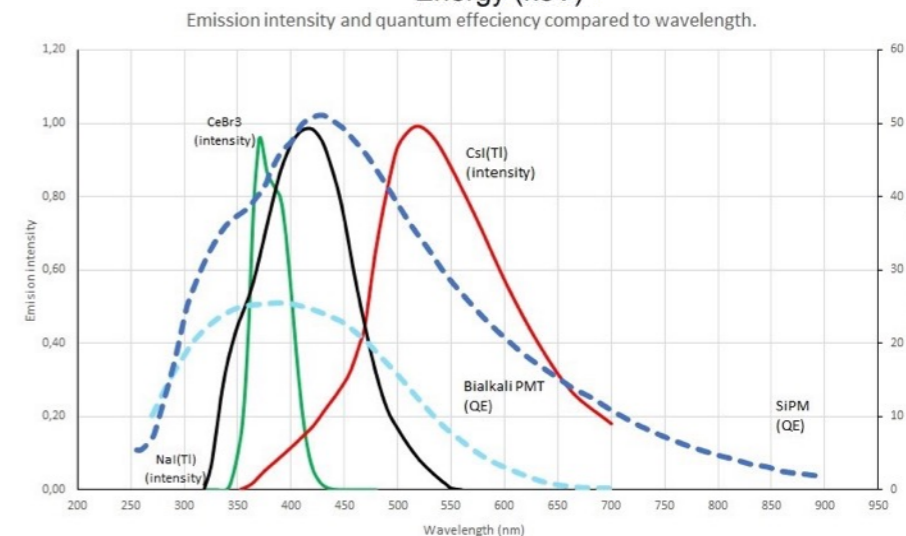
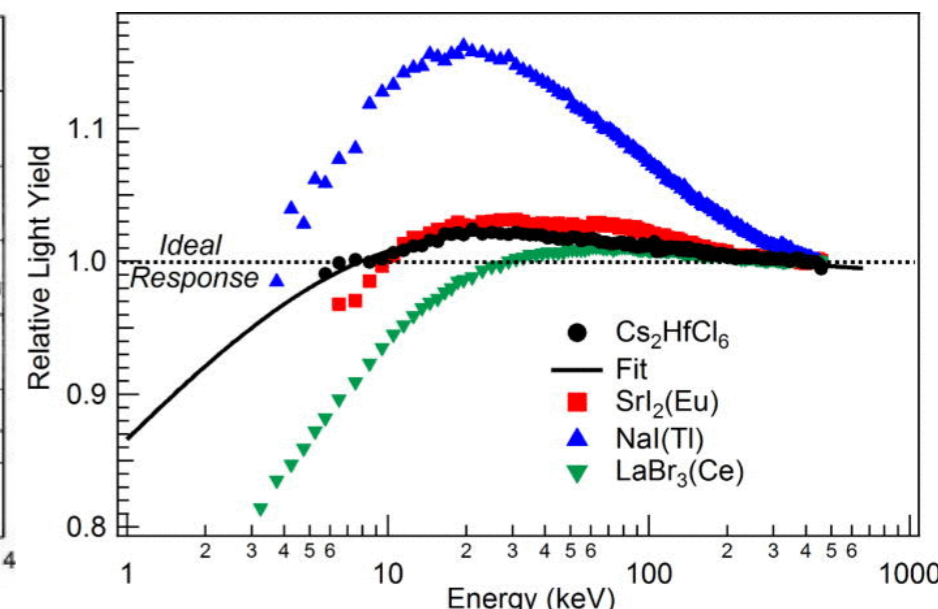
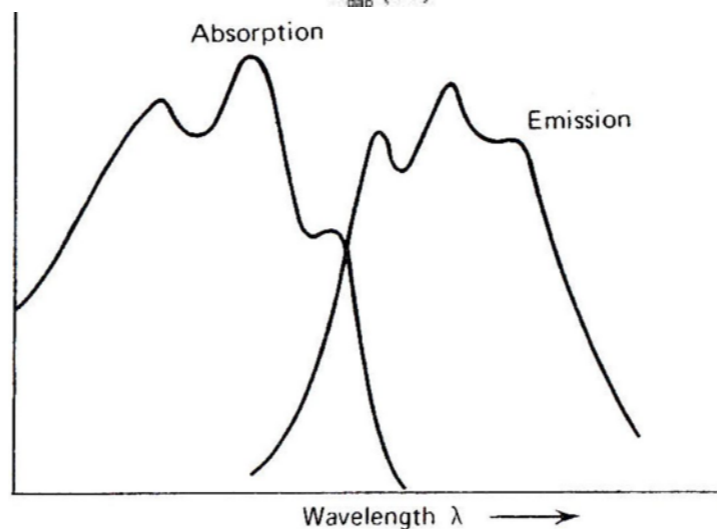
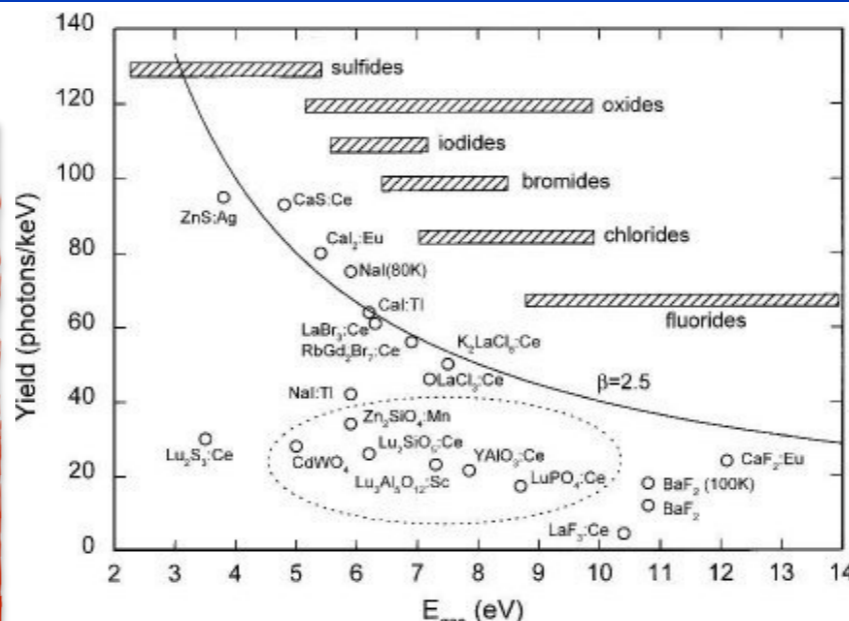




# Properties

1. Light yield
2. Linearity
3. No self-absorption
4. Emission wavelength
5. Fast
6. Optical coupling to photo-sensors

7. Scalable
8. Radio-pure!
9. Particle discrimination

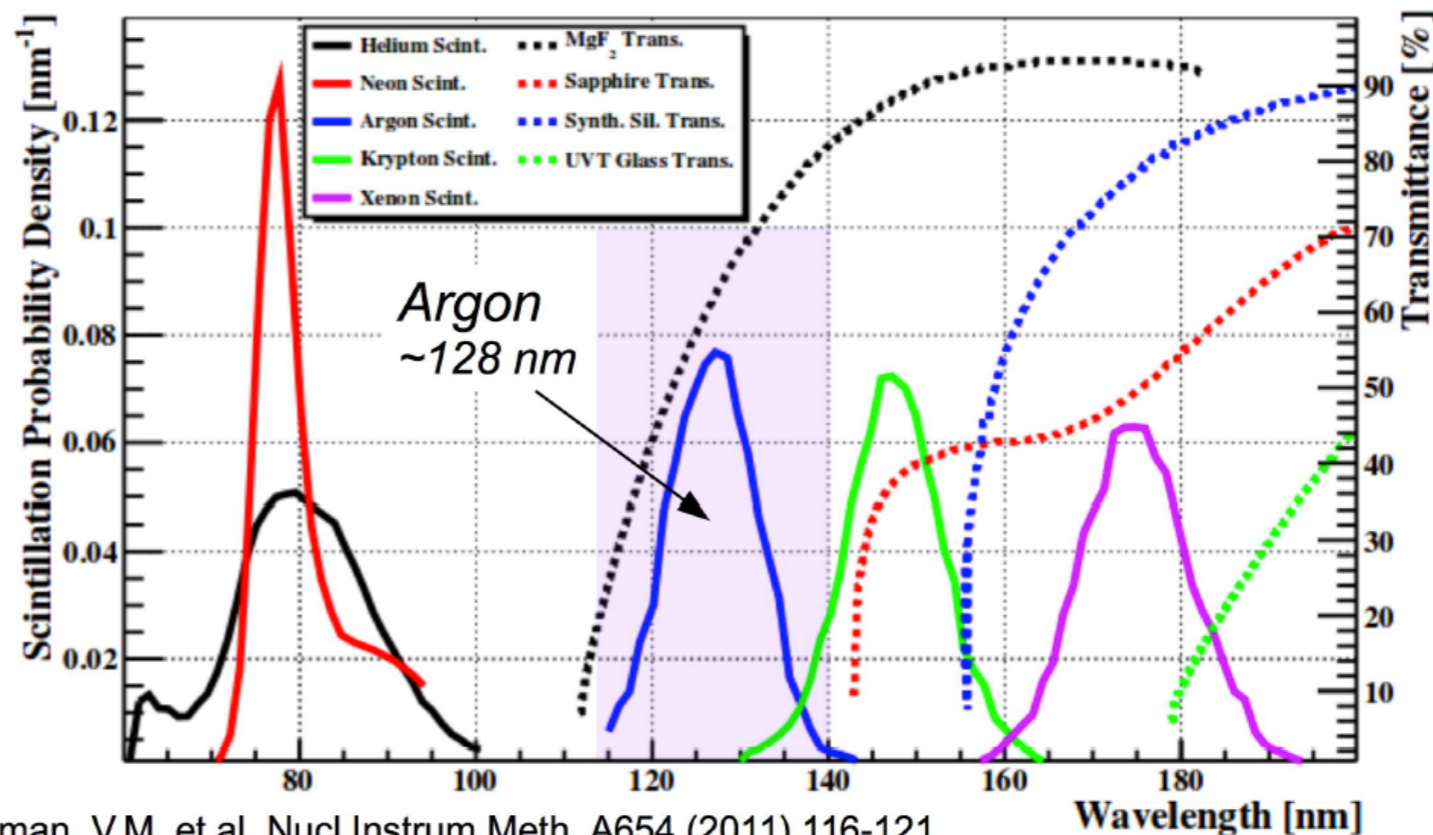




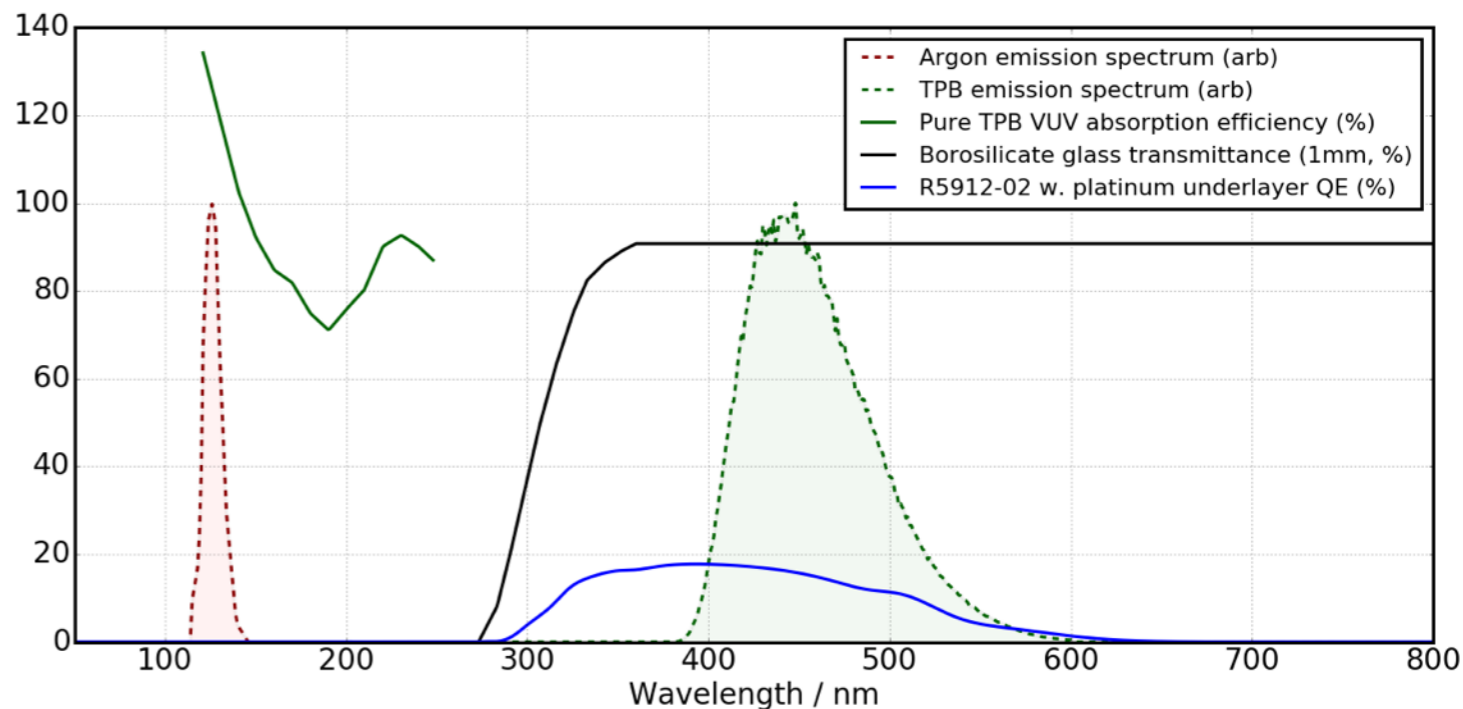
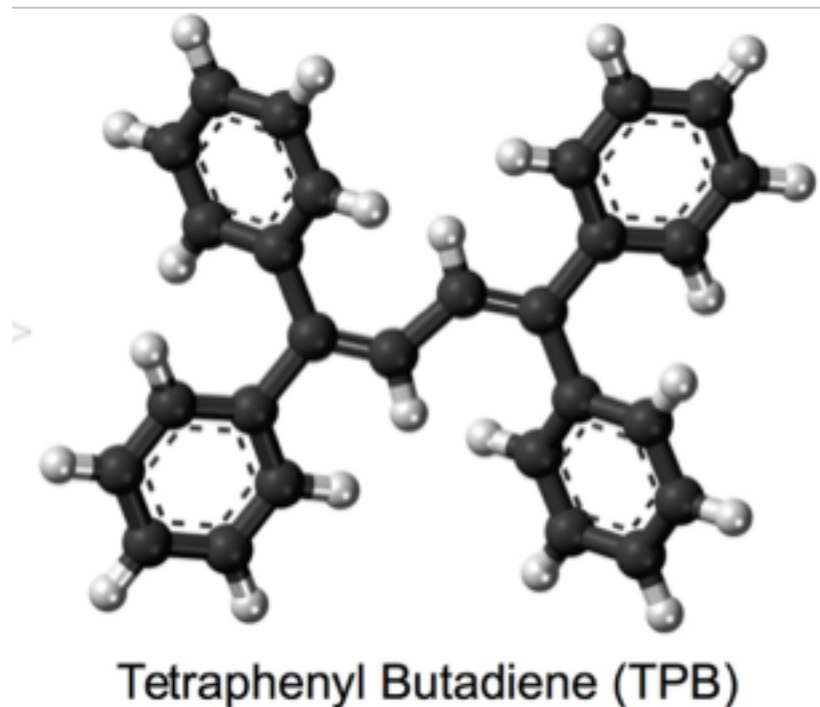
# A compromise: wavelength shifters

Any scintillator able to absorb primary scintillation light and re-emit it to more suitable wavelengths

- High conversion efficiency
- Fast



Gehman, V.M. et al. Nucl.Instrum.Meth. A654 (2011) 116-121

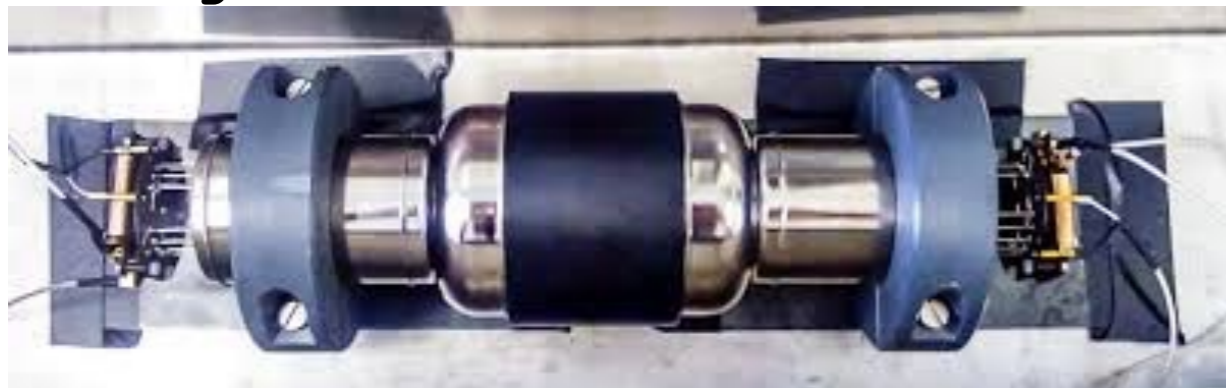




# Ultra-pure scintillators for DM searches

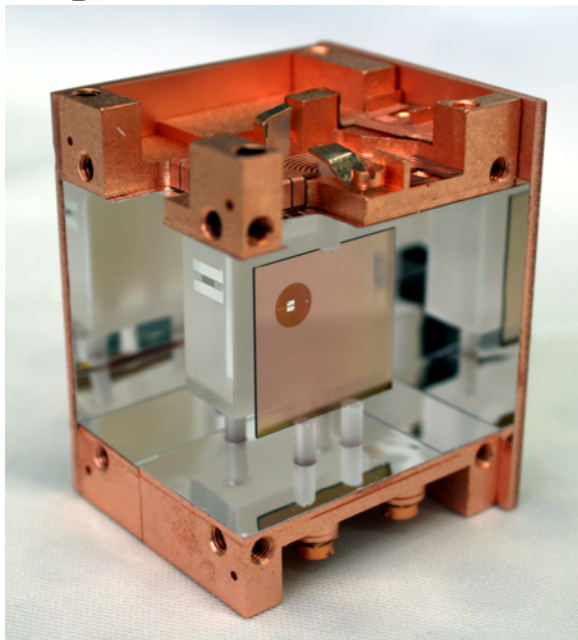
## Crystals

Room temperature:  
light measured with PMTs

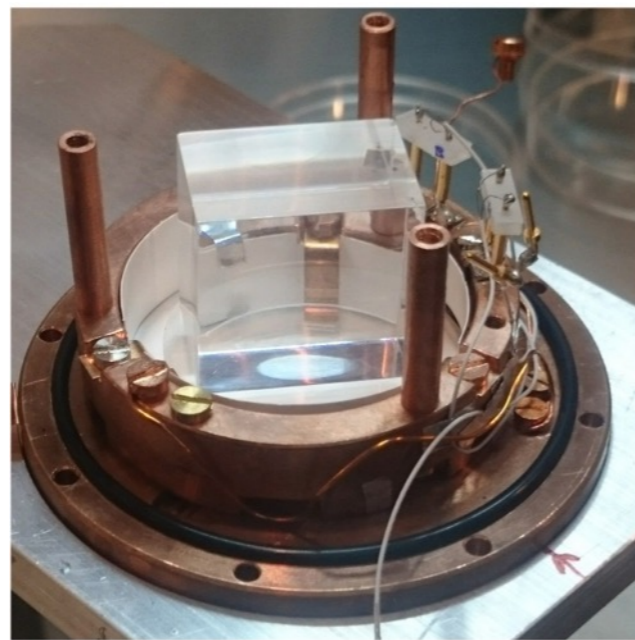


DAMA/LIBRA, ANAIS: NaI  
KIMS: CsI

Cryogenic (<20mK):  
light measured with calorimeters

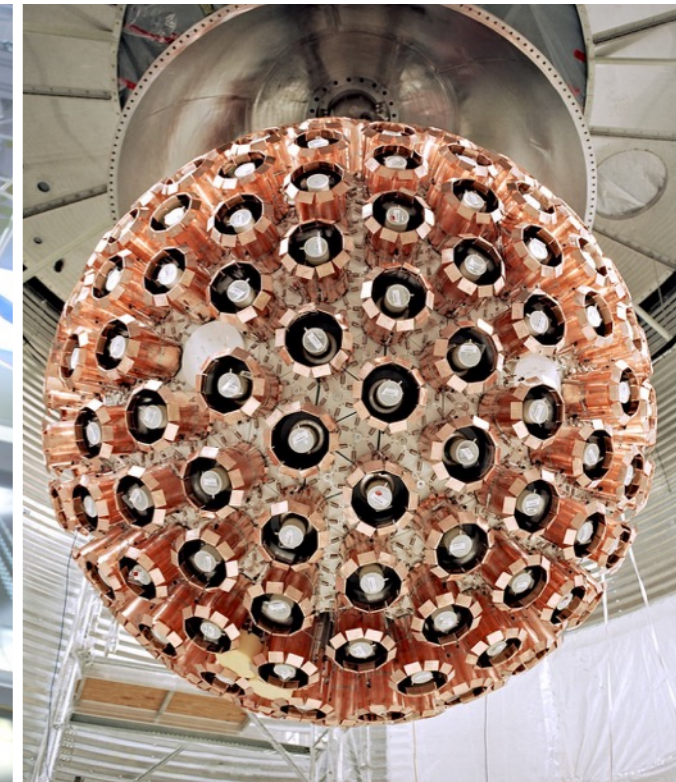
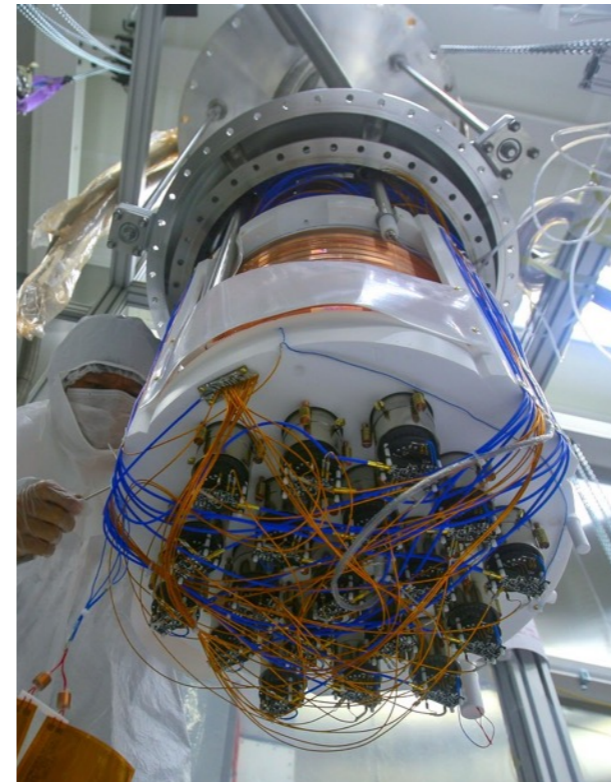


CRESST:  $\text{CaWO}_4$



Cosinus: NaI

## Noble liquids



Xenon, LUX, PandaX: Xe  
DarkSide, DEAP, ArDM: Ar

	LXe	LAr
T (K)	165	87
WL (nm)	178	128
Shifter	No	TPB
Sensor	PMT	PMT, SiPM



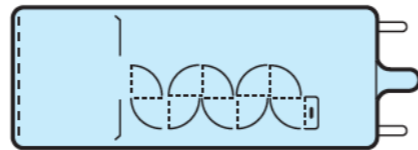
# They come in all flavours and sizes



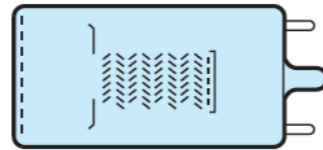
(1) Circular-cage type



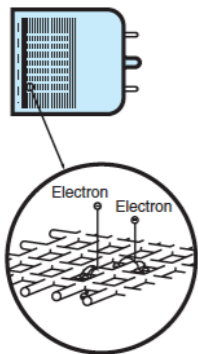
(2) Box-and-grid type



(3) Linear-focused type

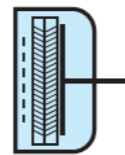


(4) Venetian blind type

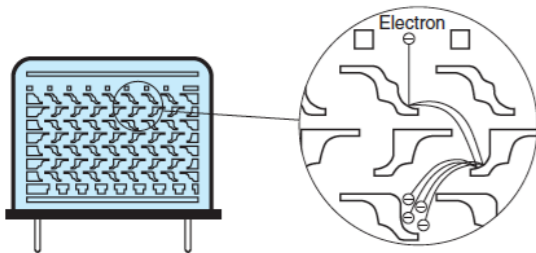


Fine-mesh

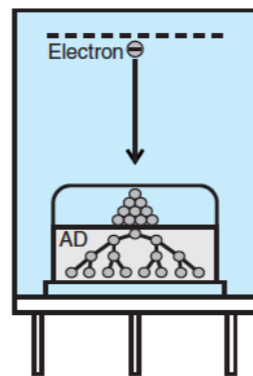
(5) Mesh type



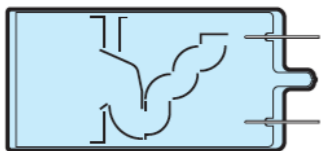
(6) MCP (Microchannel plate) type



(7) Metal channel type



(8) Electron bombardment type



(9) Box-and-line type

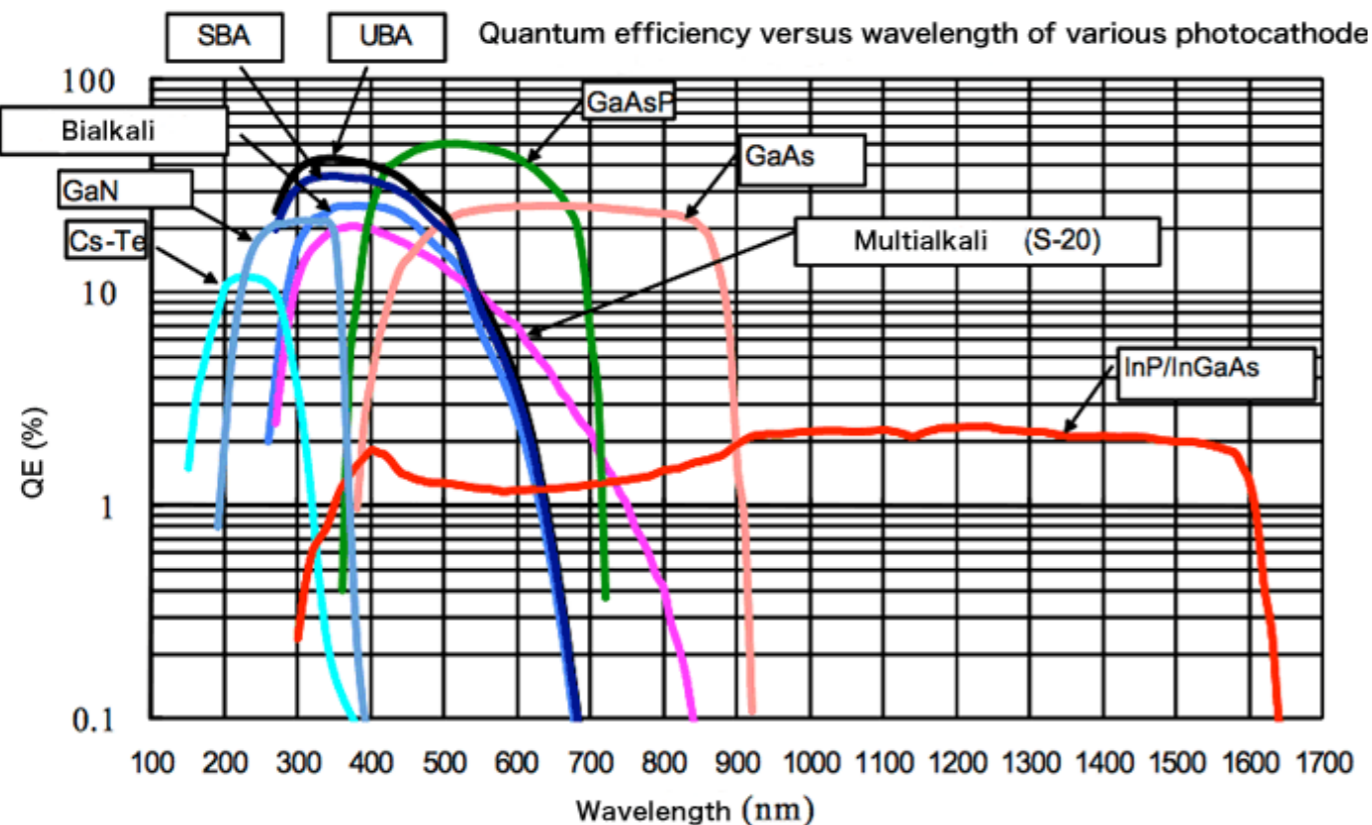
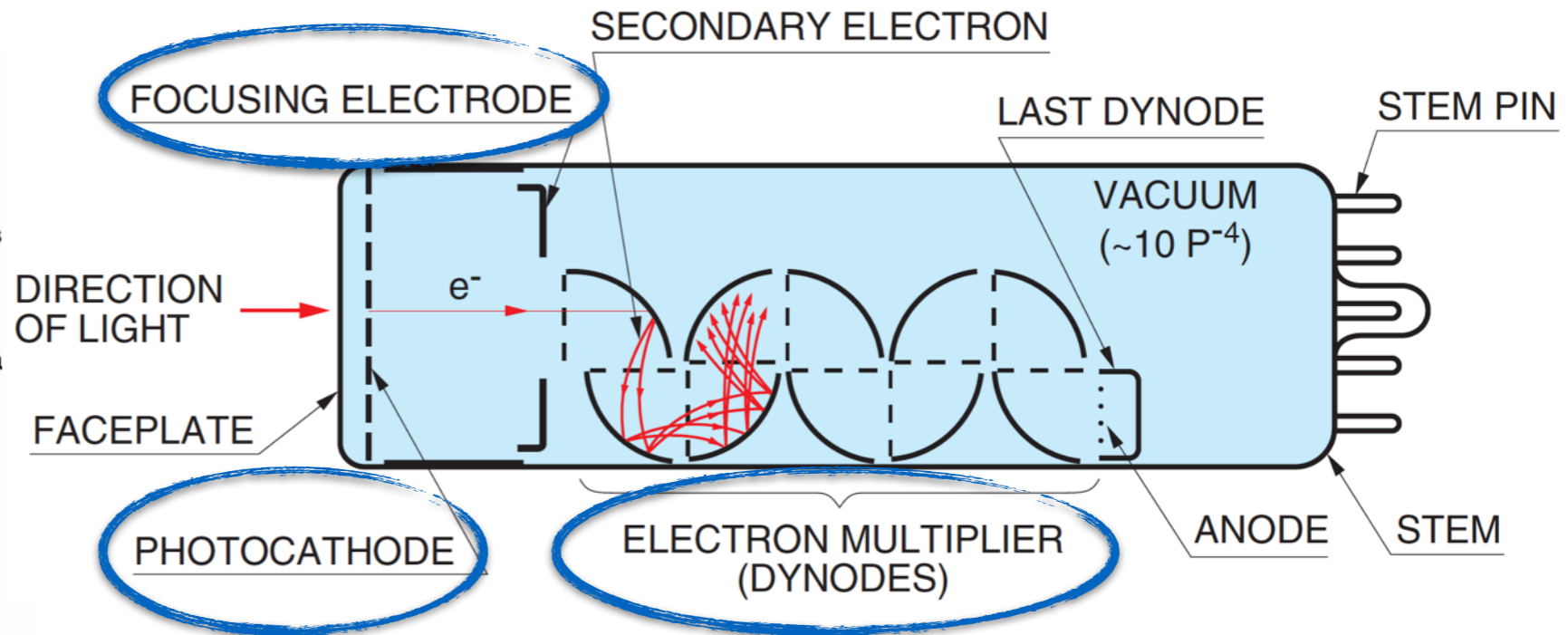
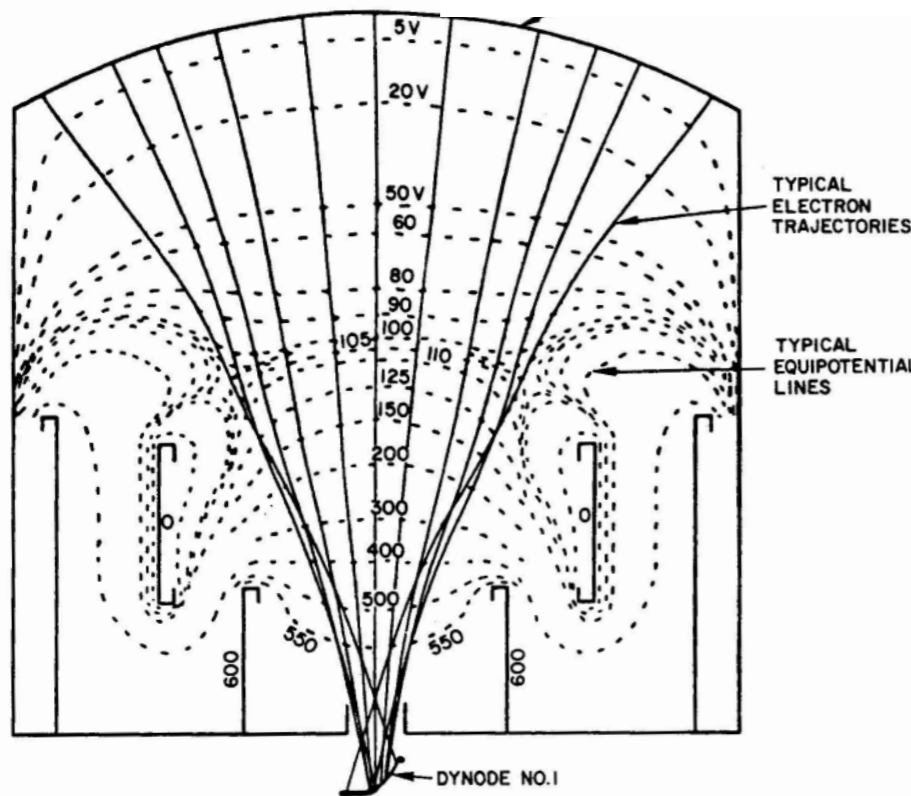


(10) Circular and linear-focused type

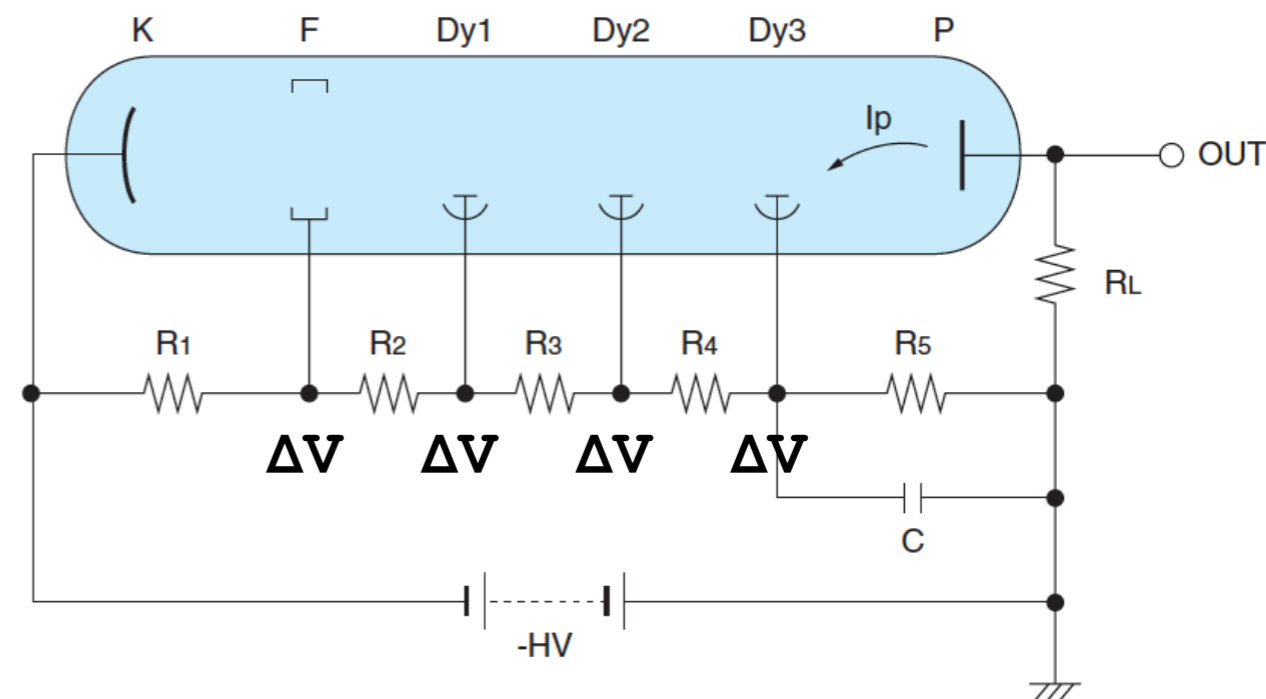




# PMT structure



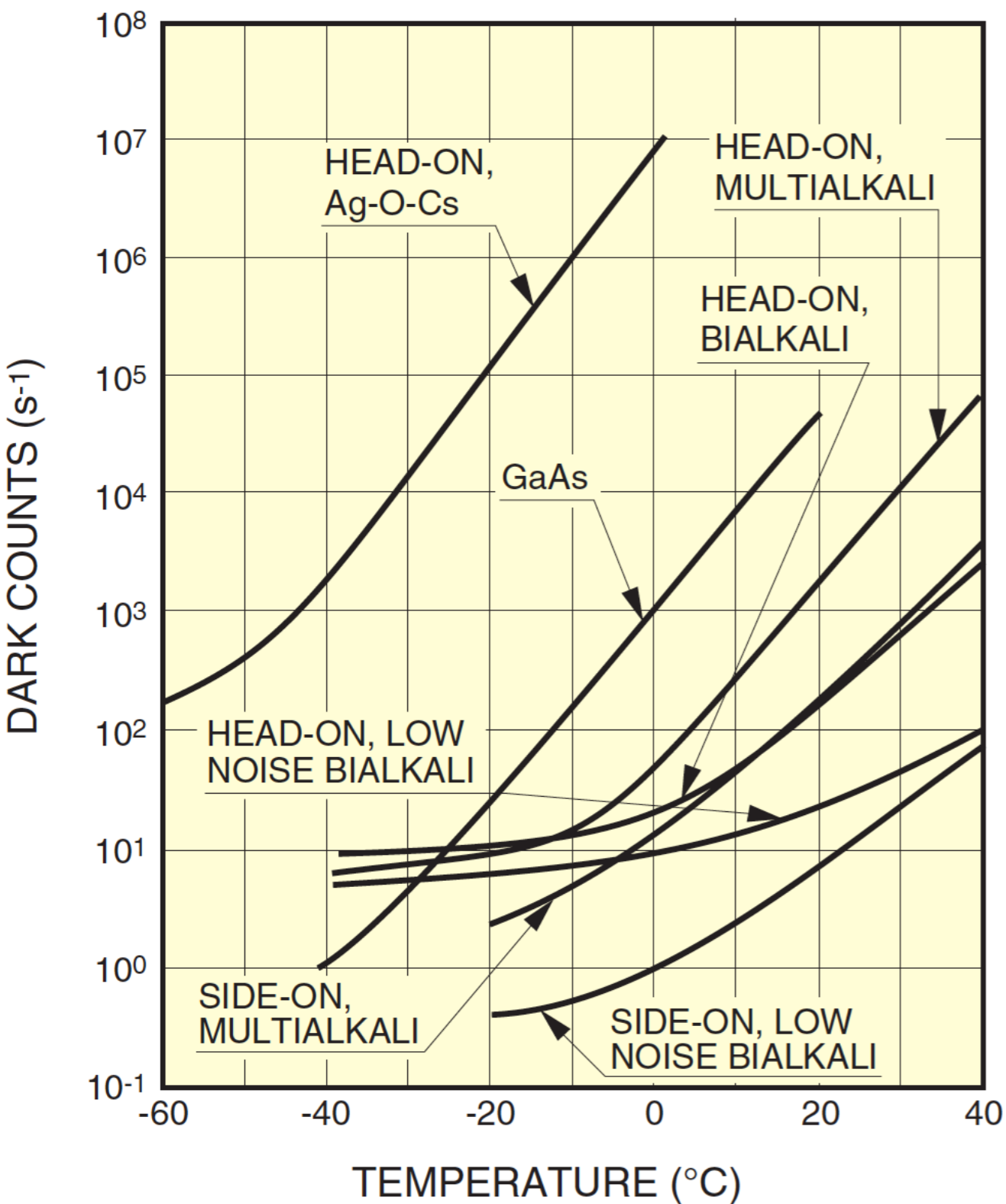
Dynodes  $\Delta V$  accelerates  $e^-$



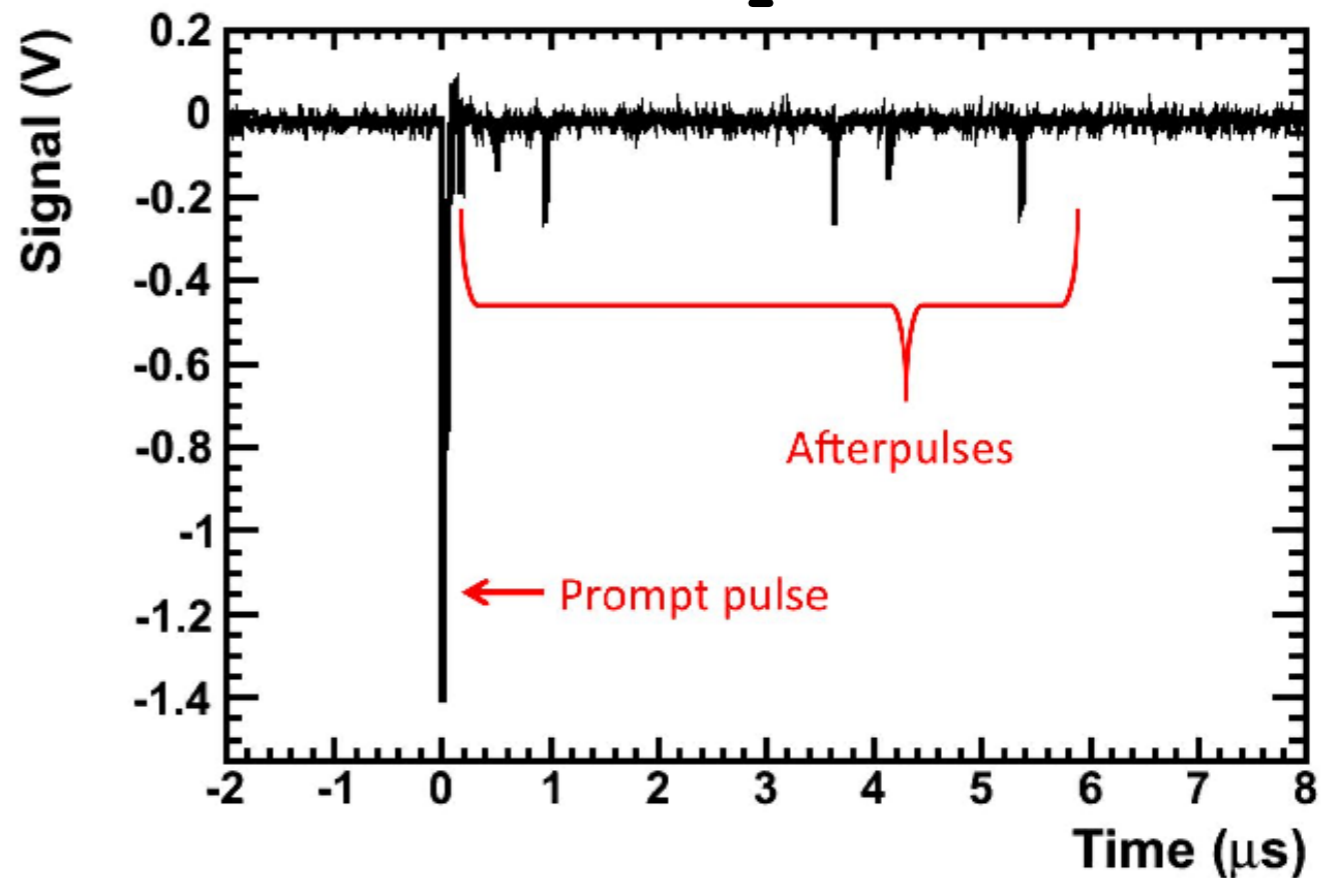


# PMT Noises

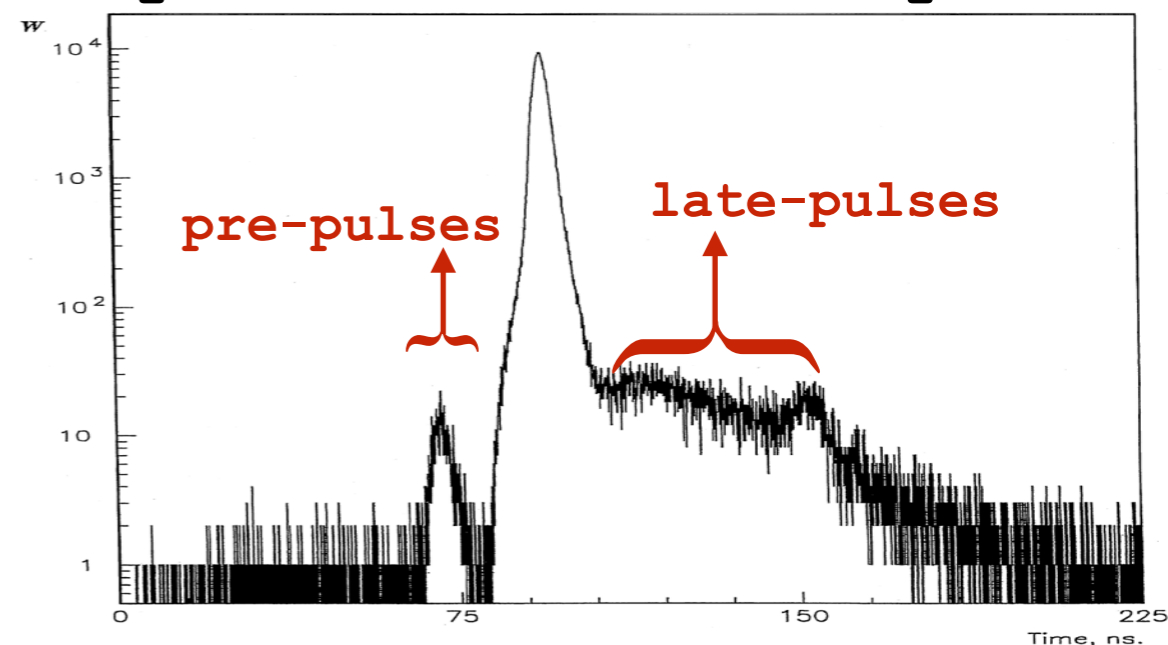
## Dark Count Rate



## After pulses



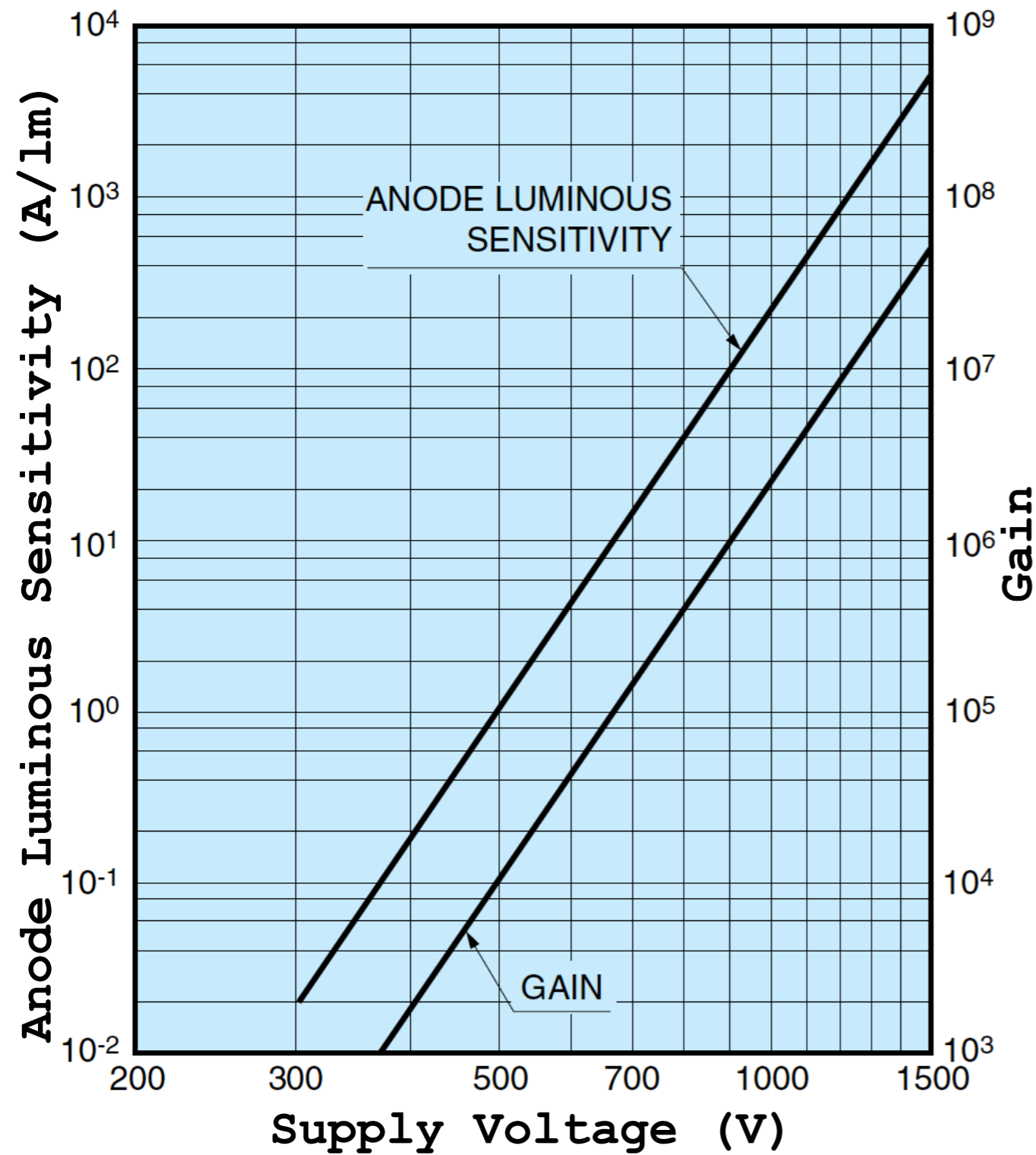
## Prepulses and late-pulses



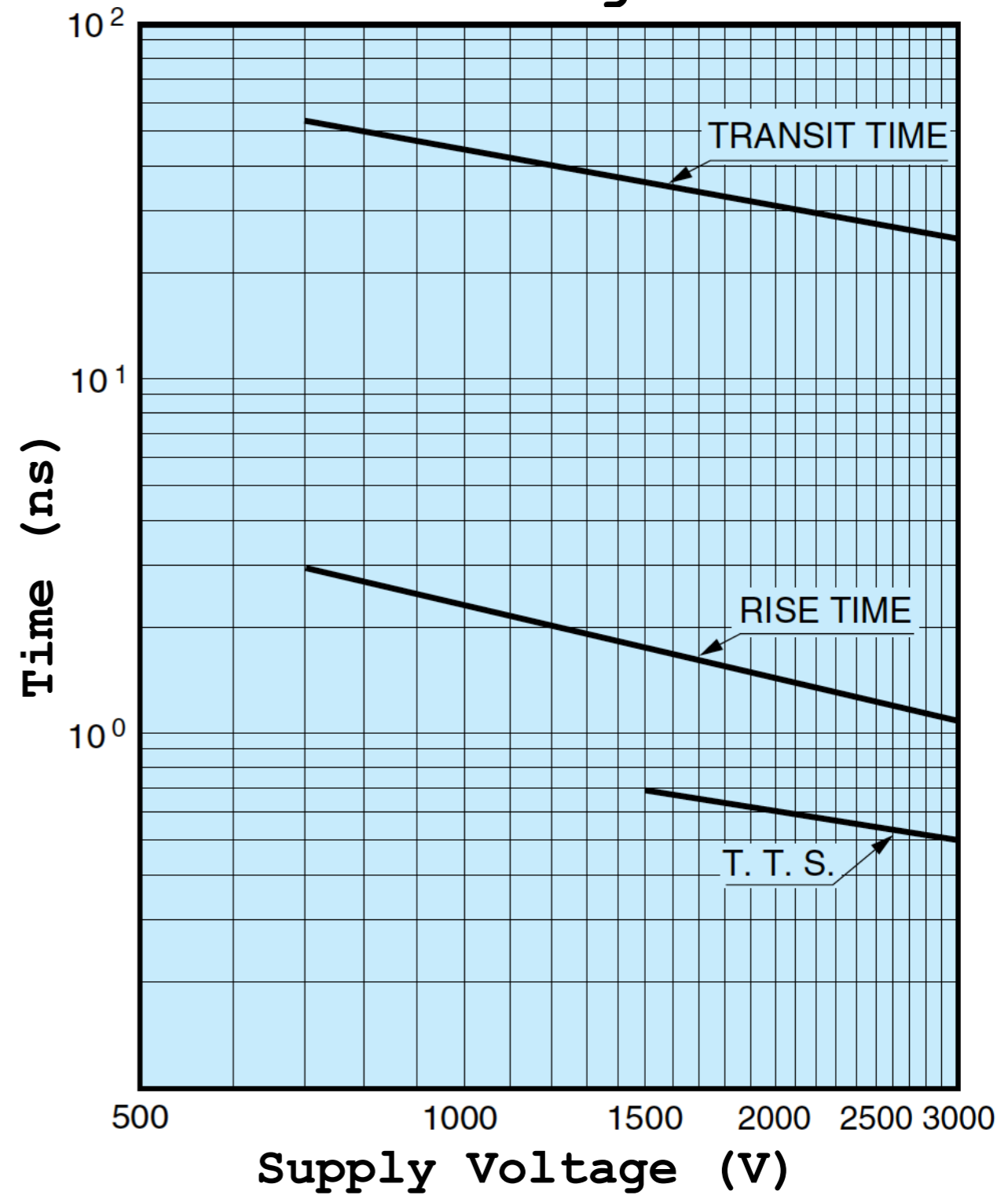


# PMT common features

## Gain



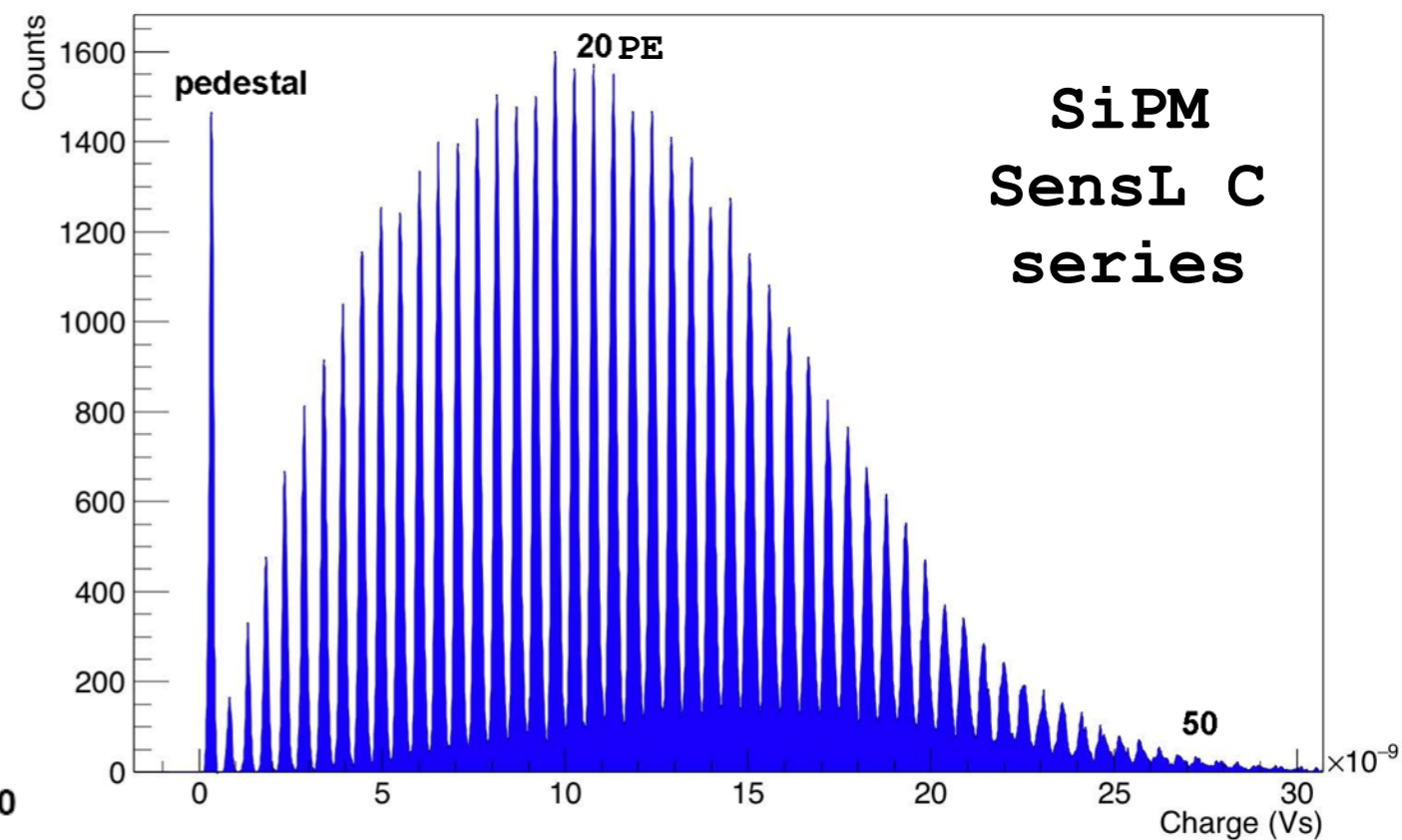
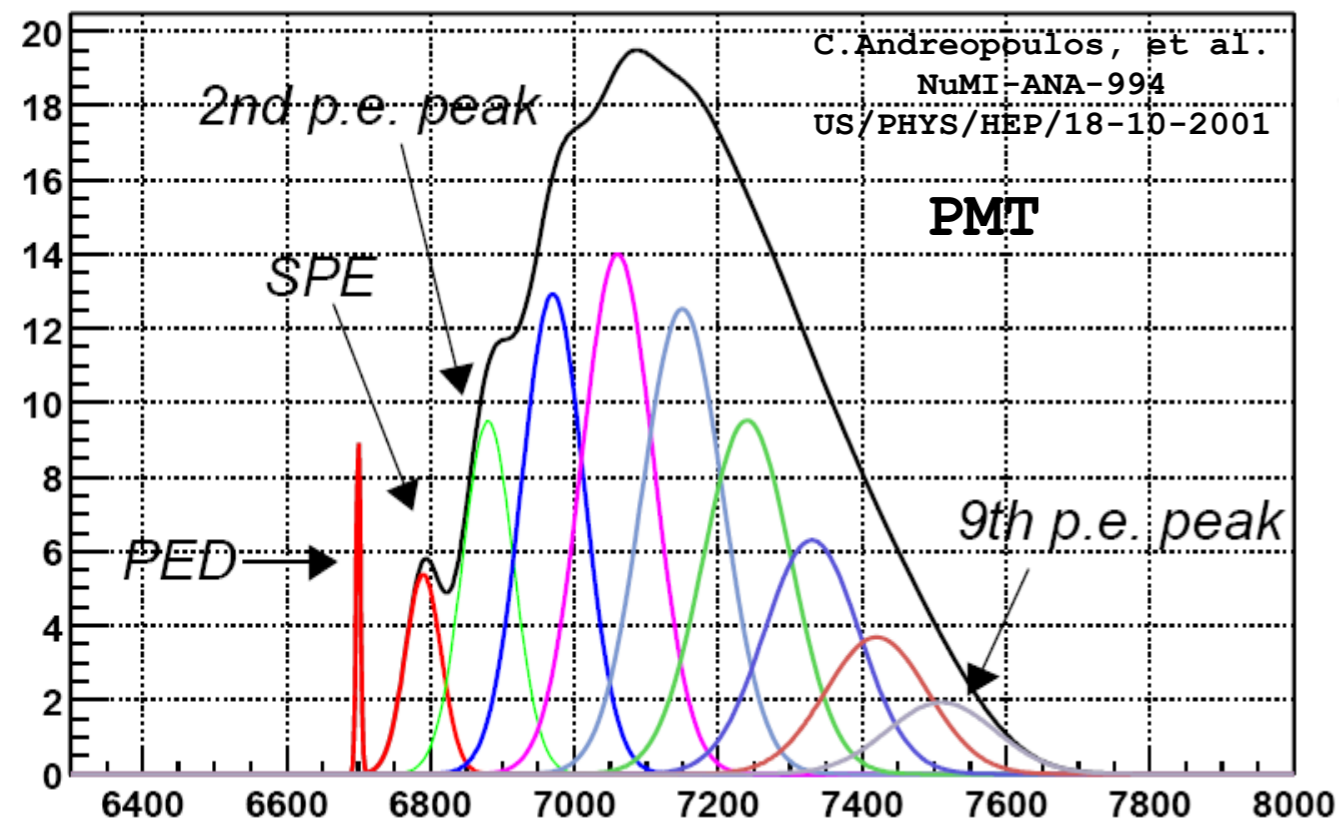
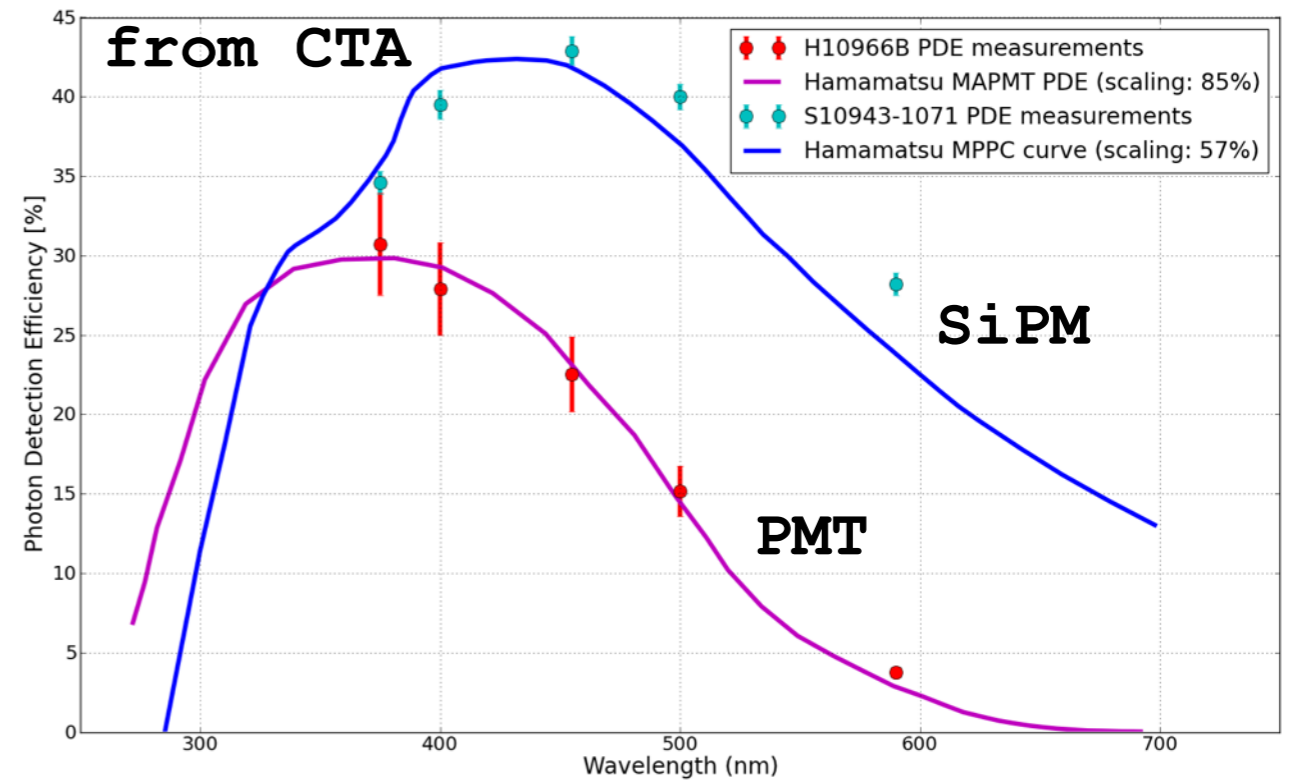
## Timing





# SiPMs: why bet on them?

1. Radio-purity
2. Resolution
3. PDE
4. Versatility



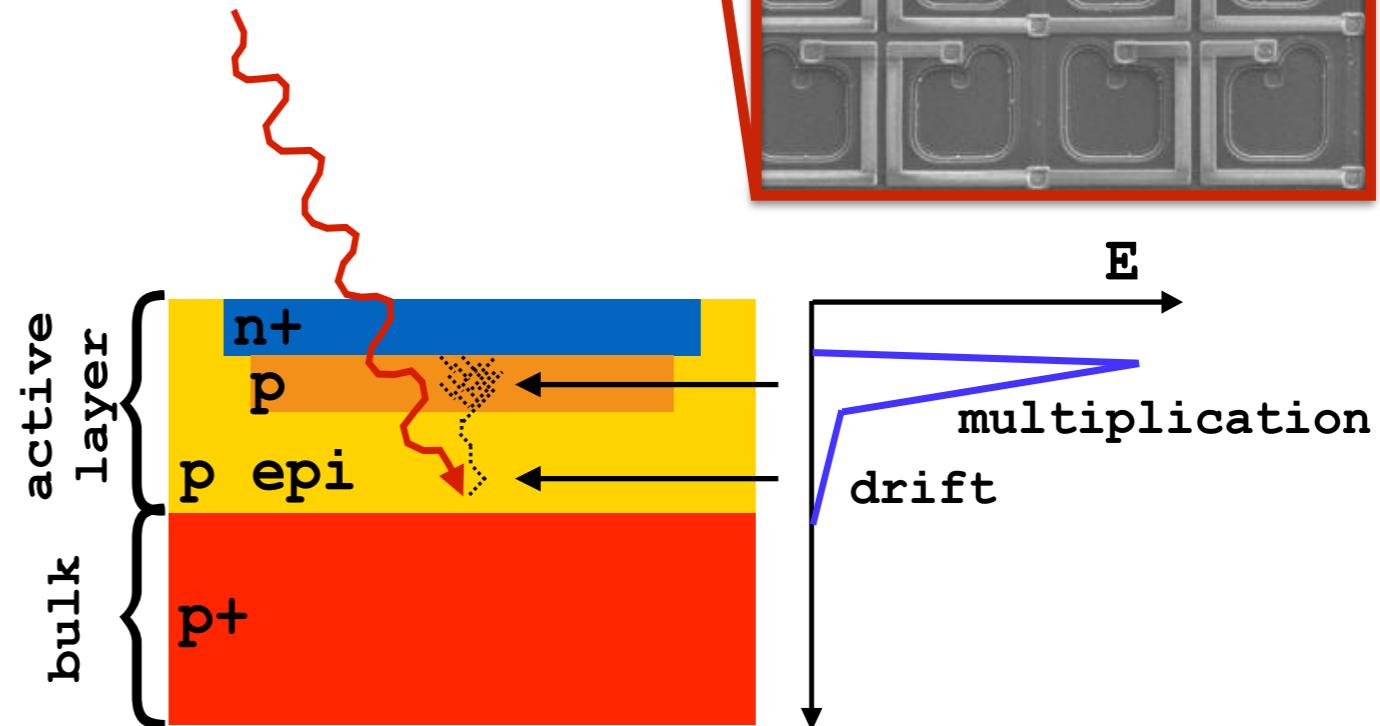
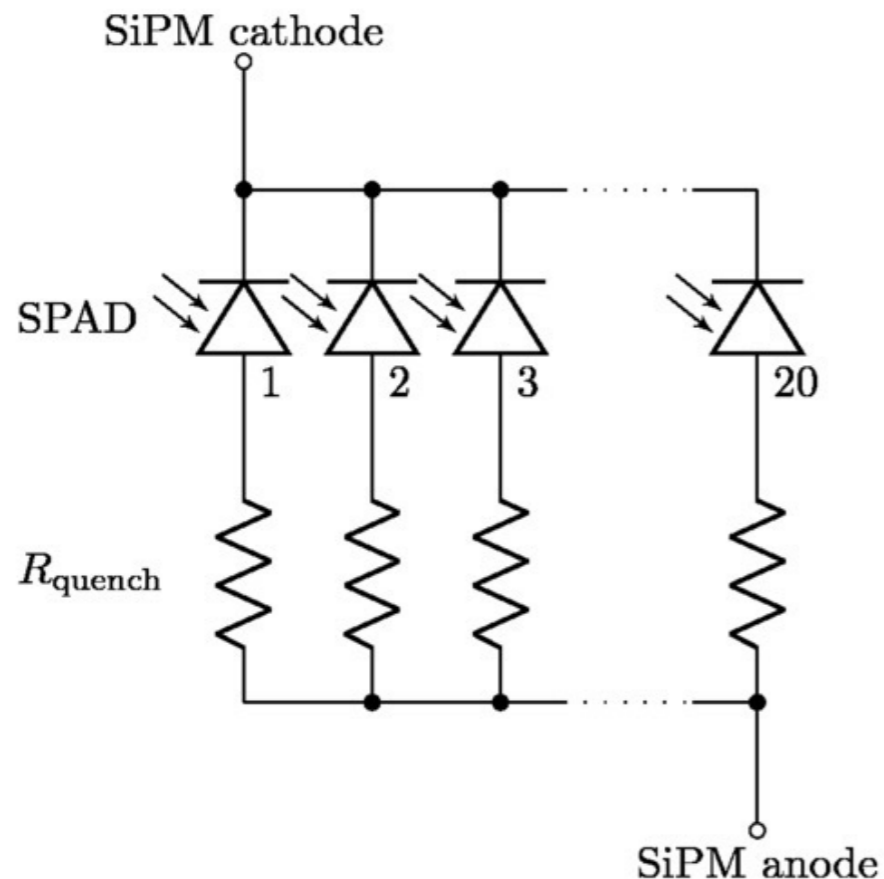
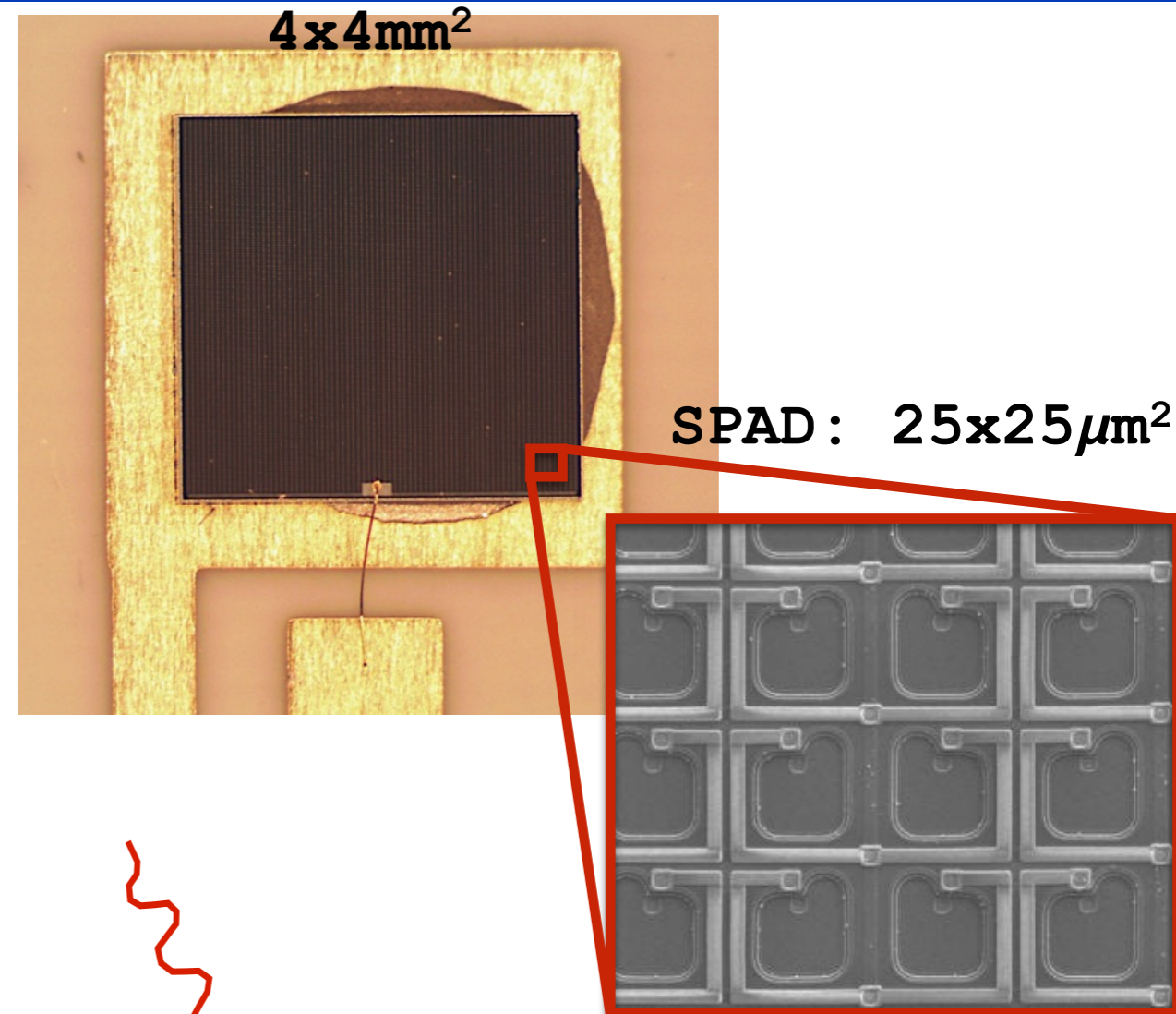


# SiPMs

SiPM: matrix of SPADs mounted in parallel

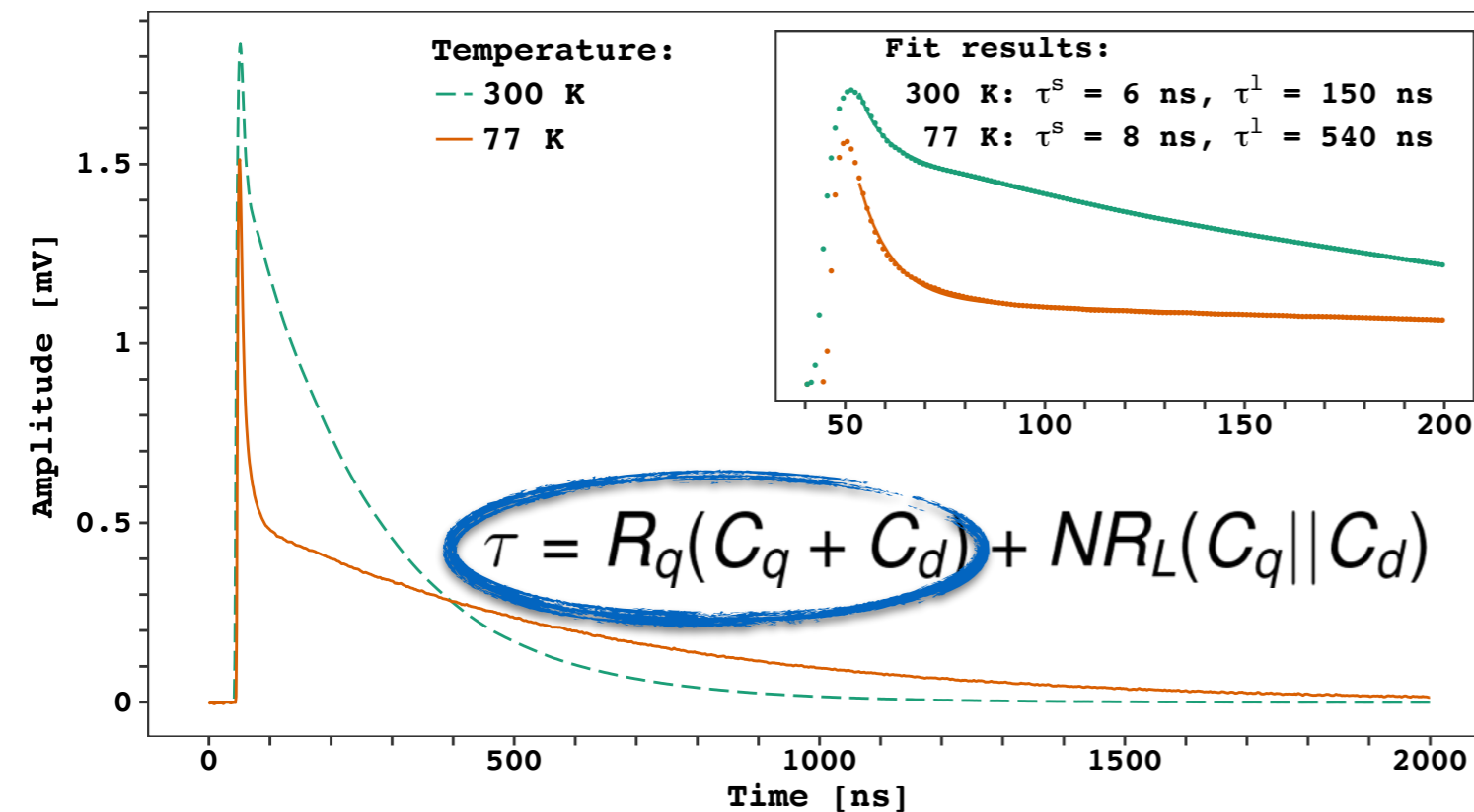
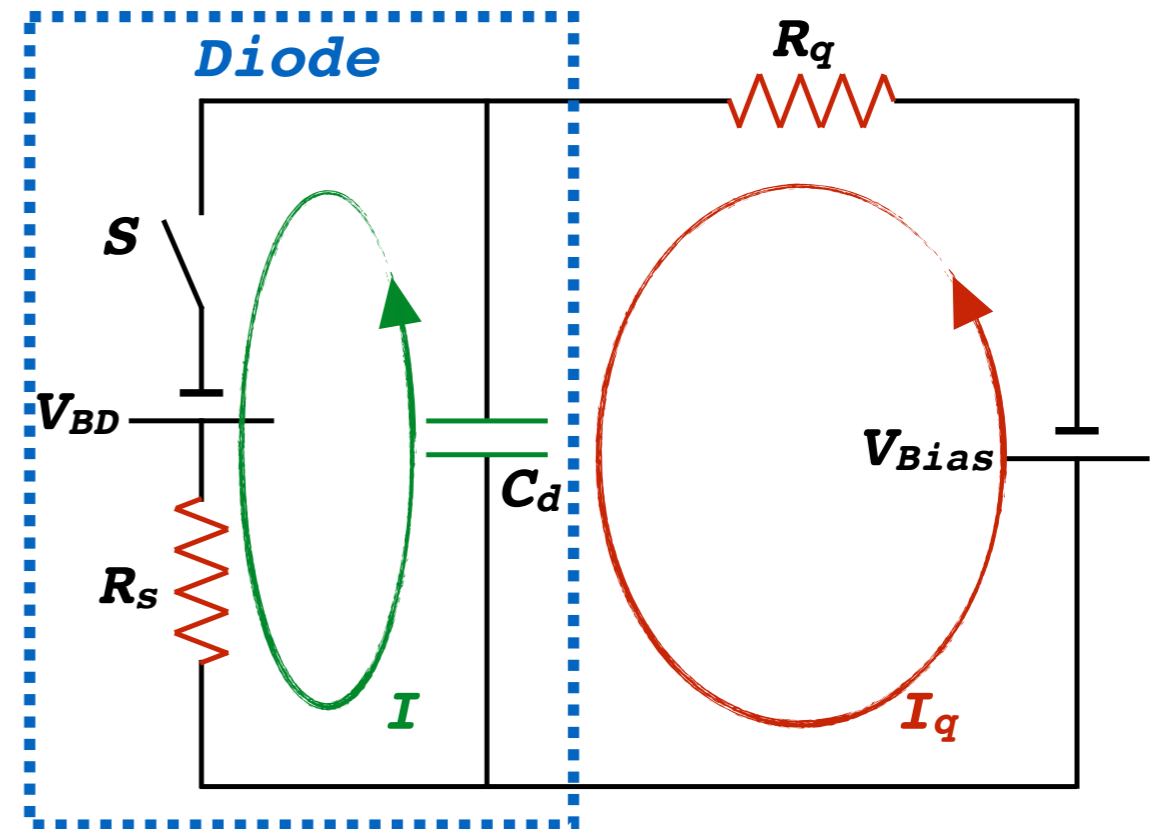
SPAD: Avalanche PhotoDiode operated in geiger mode

Passive avalanche quenching through  $R_q \sim M\Omega$  resistor



# Signal formation in SiPMs

- SPAD equivalent to 2 RC meshes
- Important parameters: diode capacitance ( $C_d$ ) and resistance ( $R_s$ ), and quenching resistor ( $R_q$ )

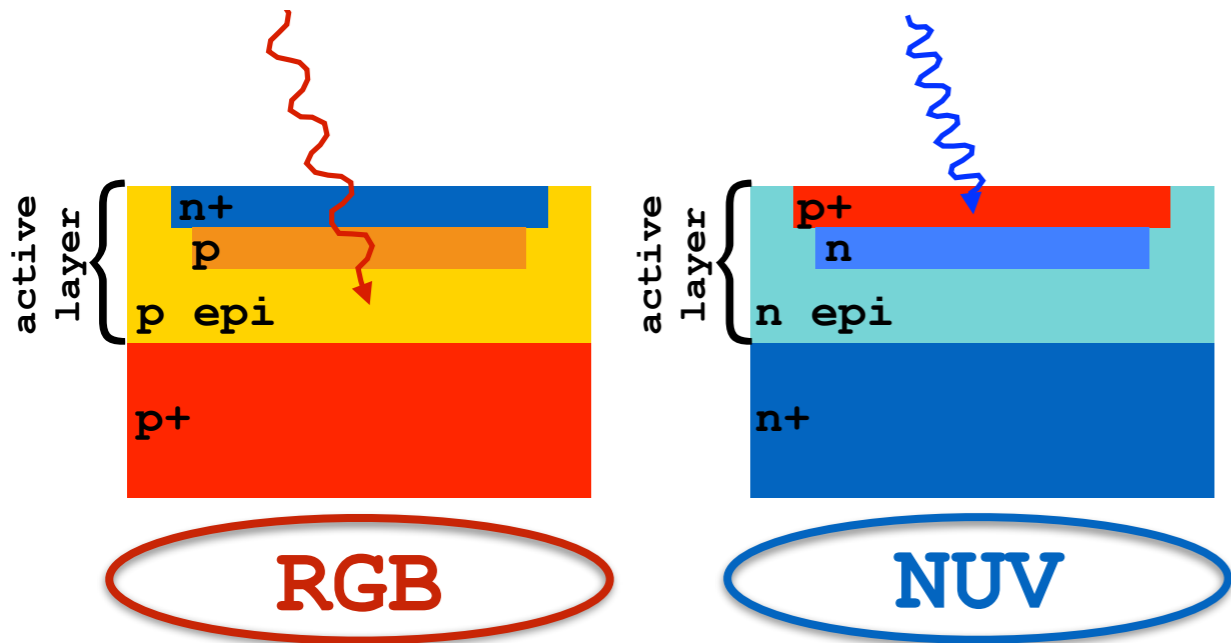


1. Fast peak:  $C_d$  discharge through  $R_s$
2. Slow exponential tail:  $C_d$  recharge through  $R_q$

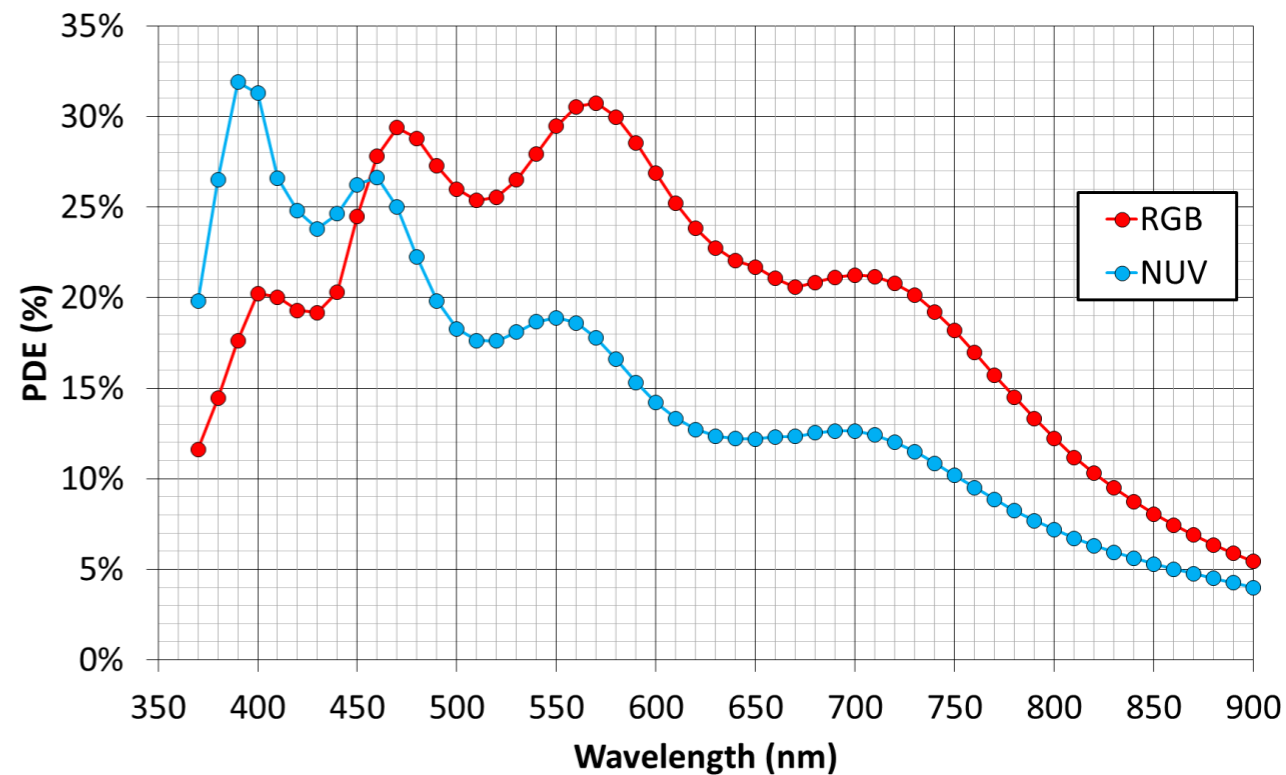


# PDE

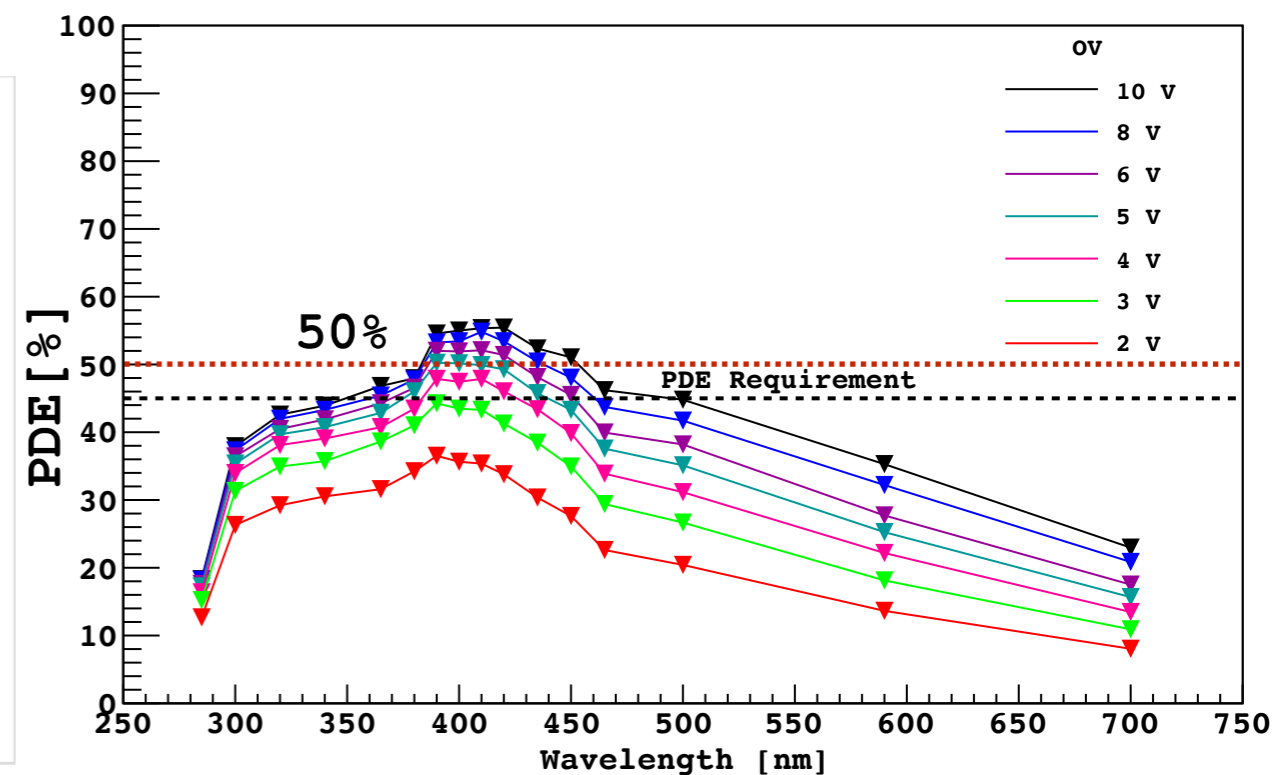
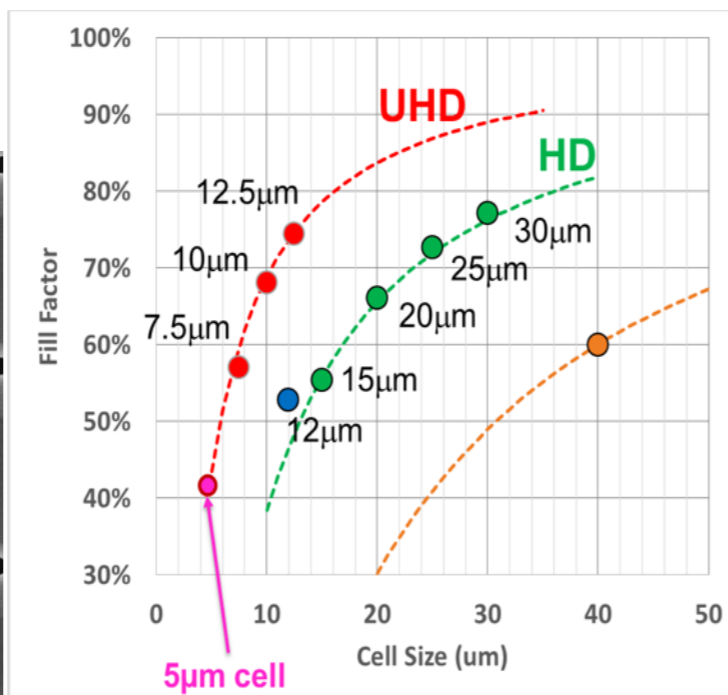
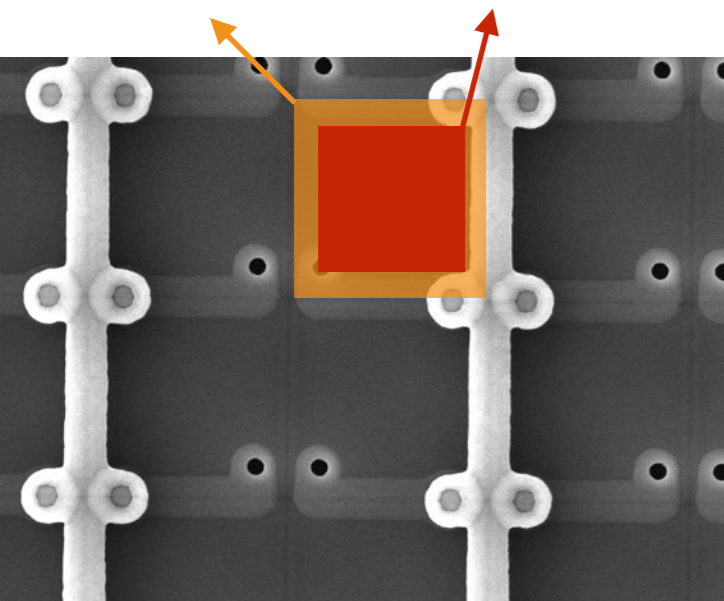
$$PDE = QE \cdot P_{01} \cdot FF$$



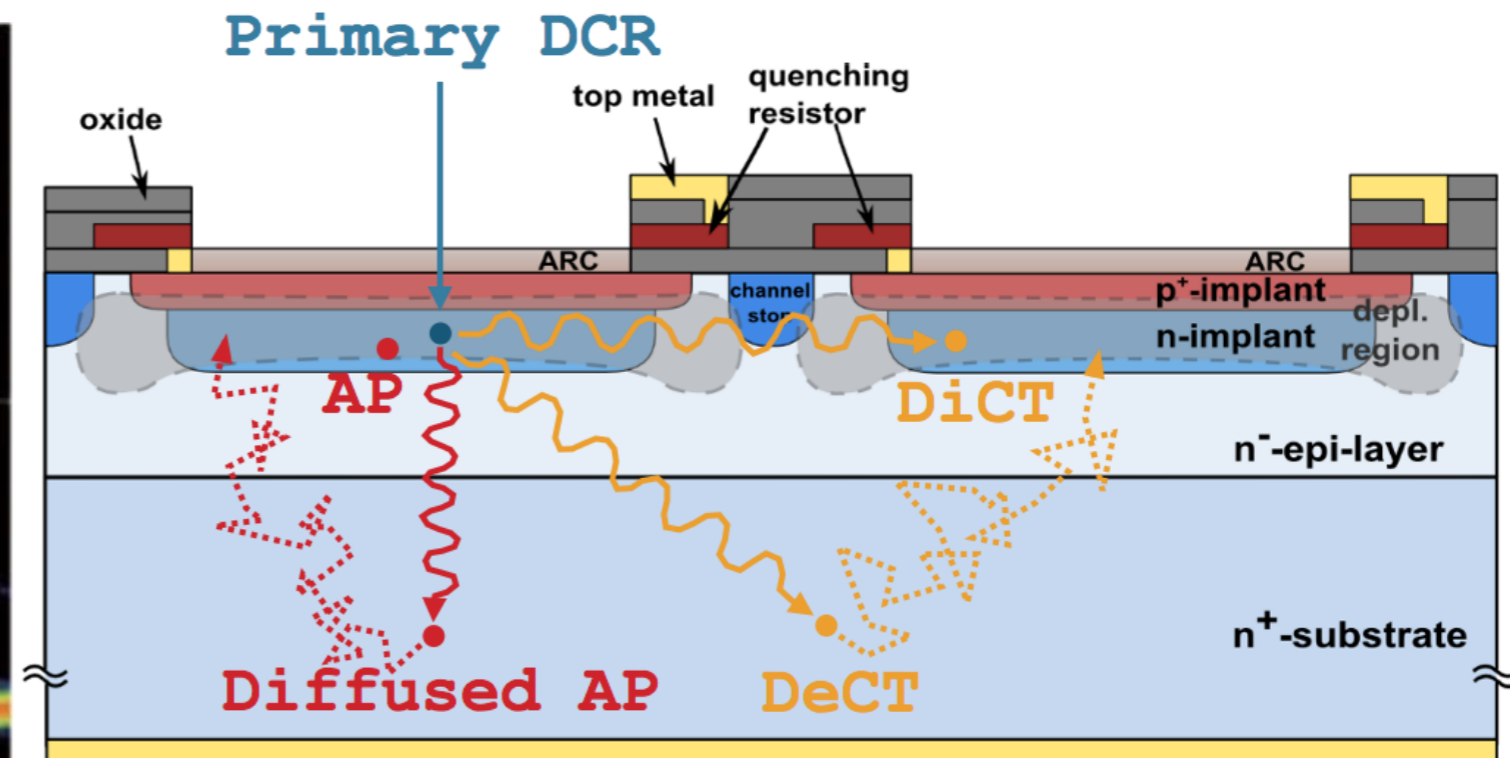
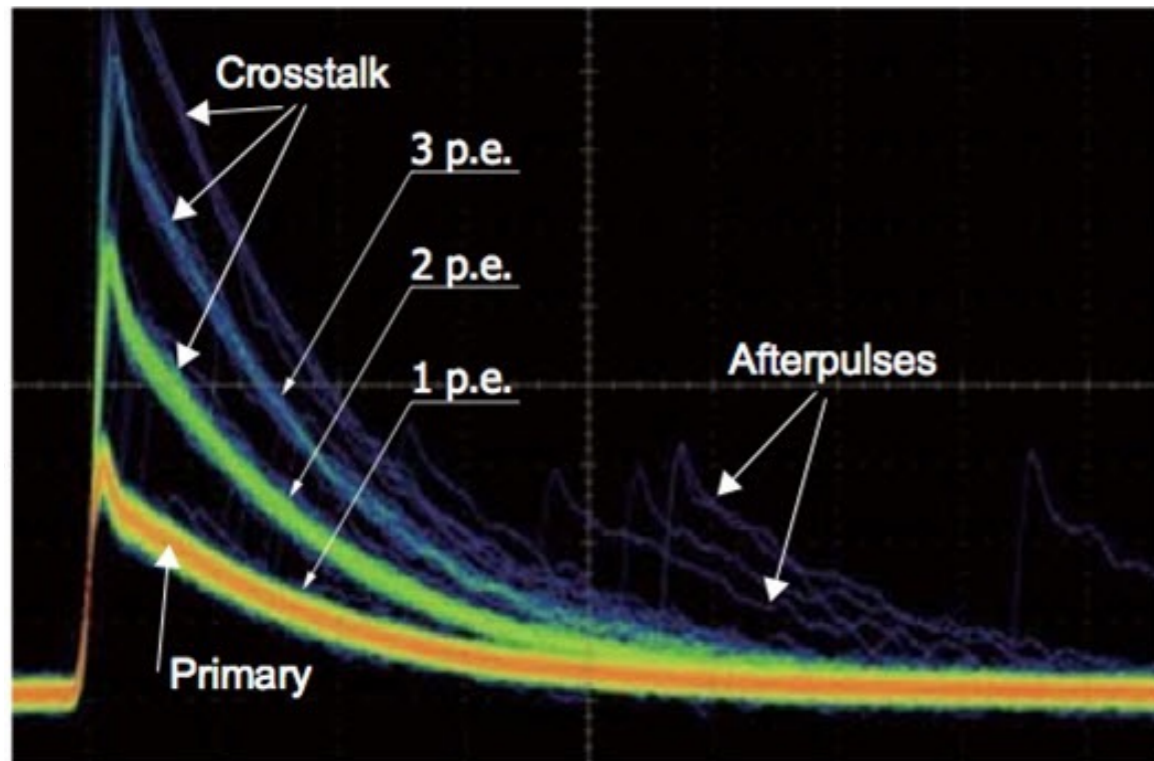
PDE @ 4.5 V OV: technology comparison



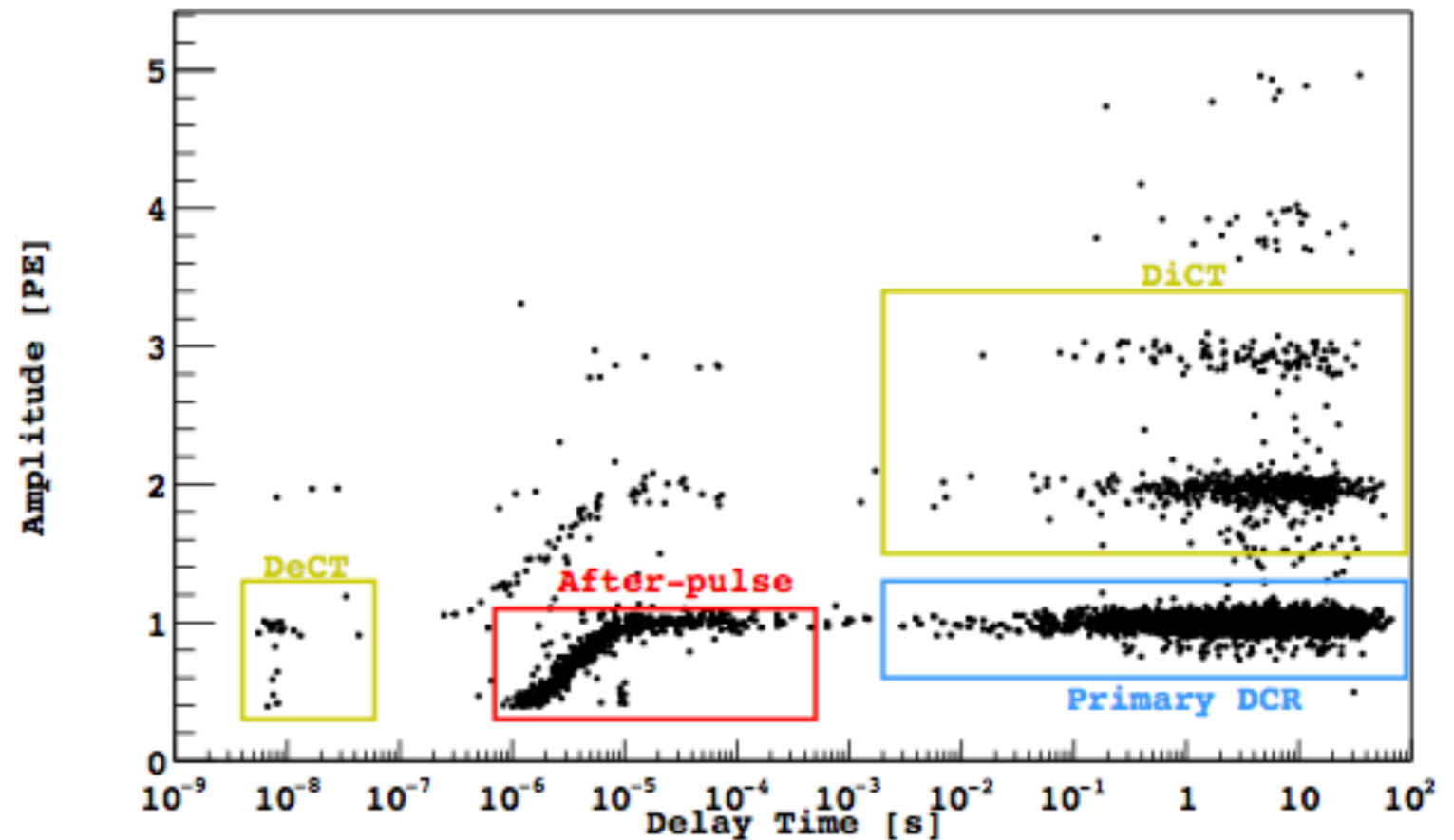
Total Area      Active Area



# SiPM technology: noises

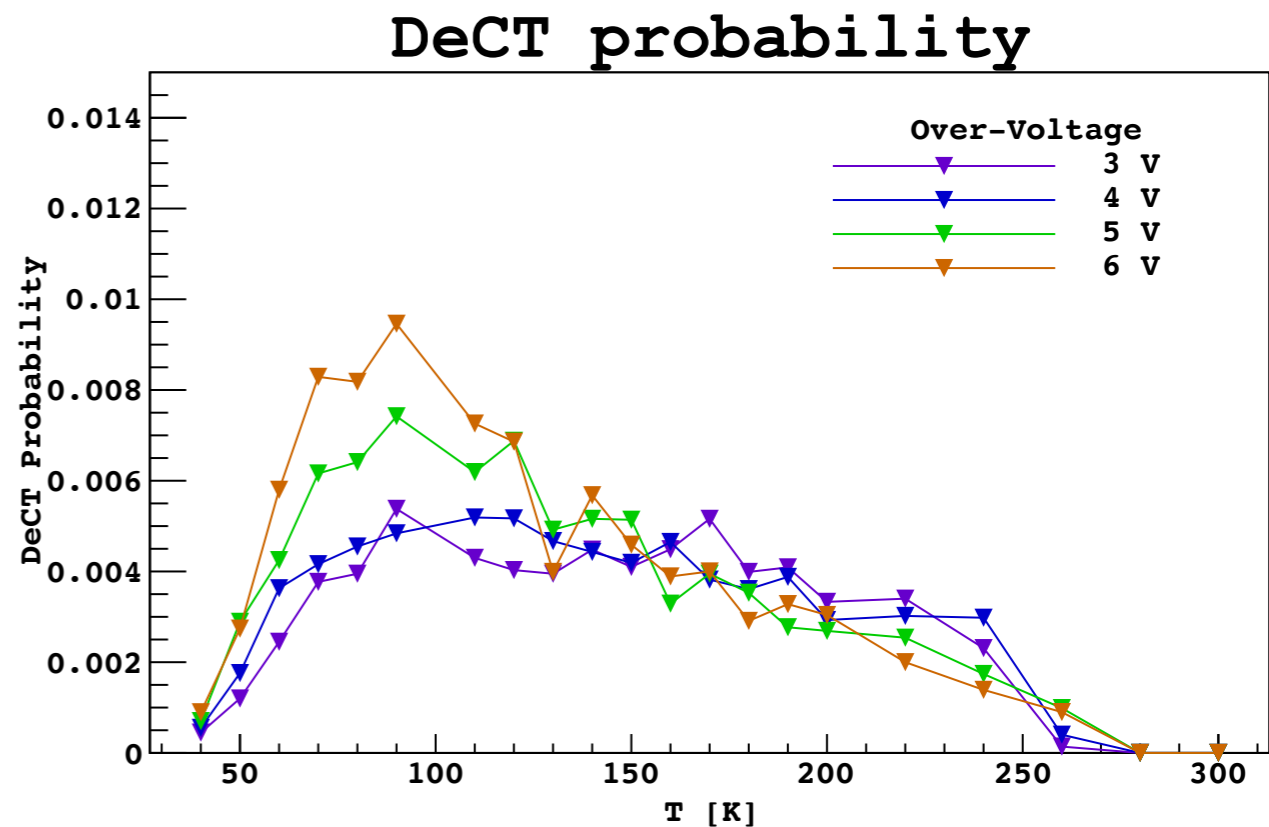
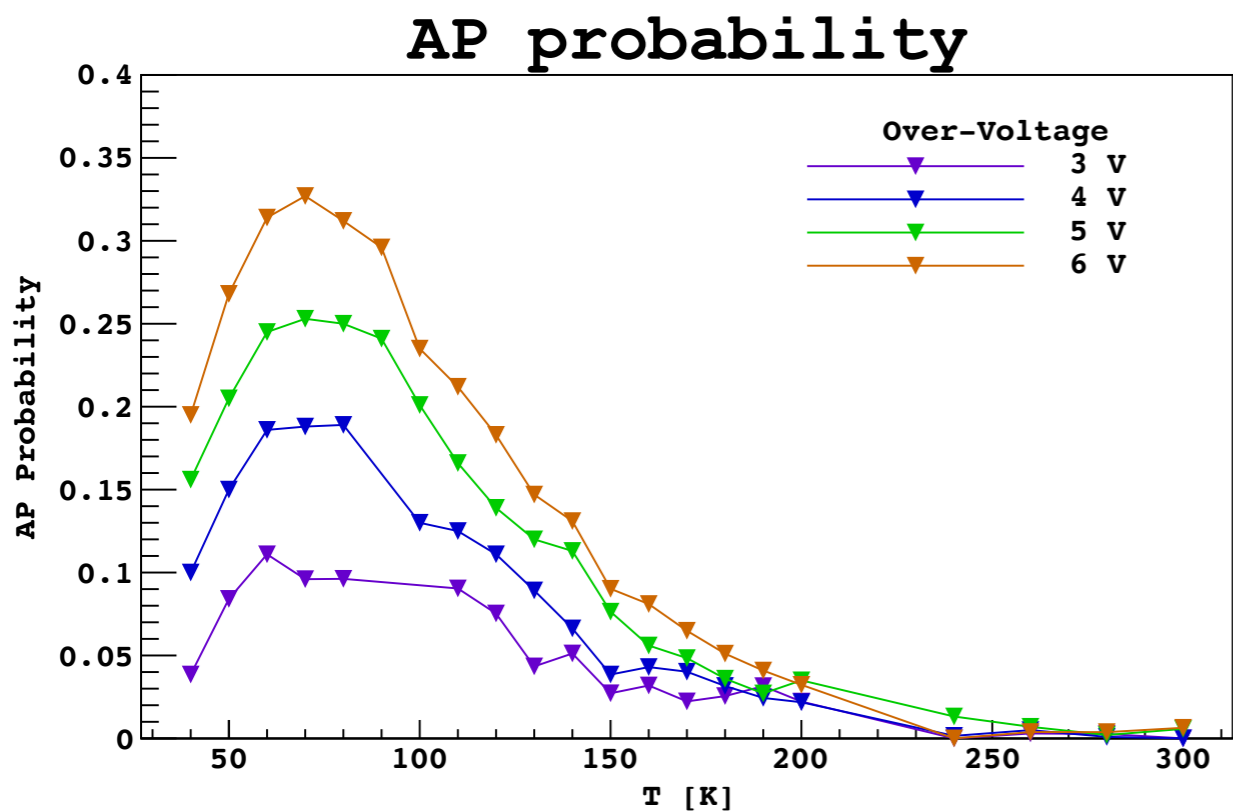
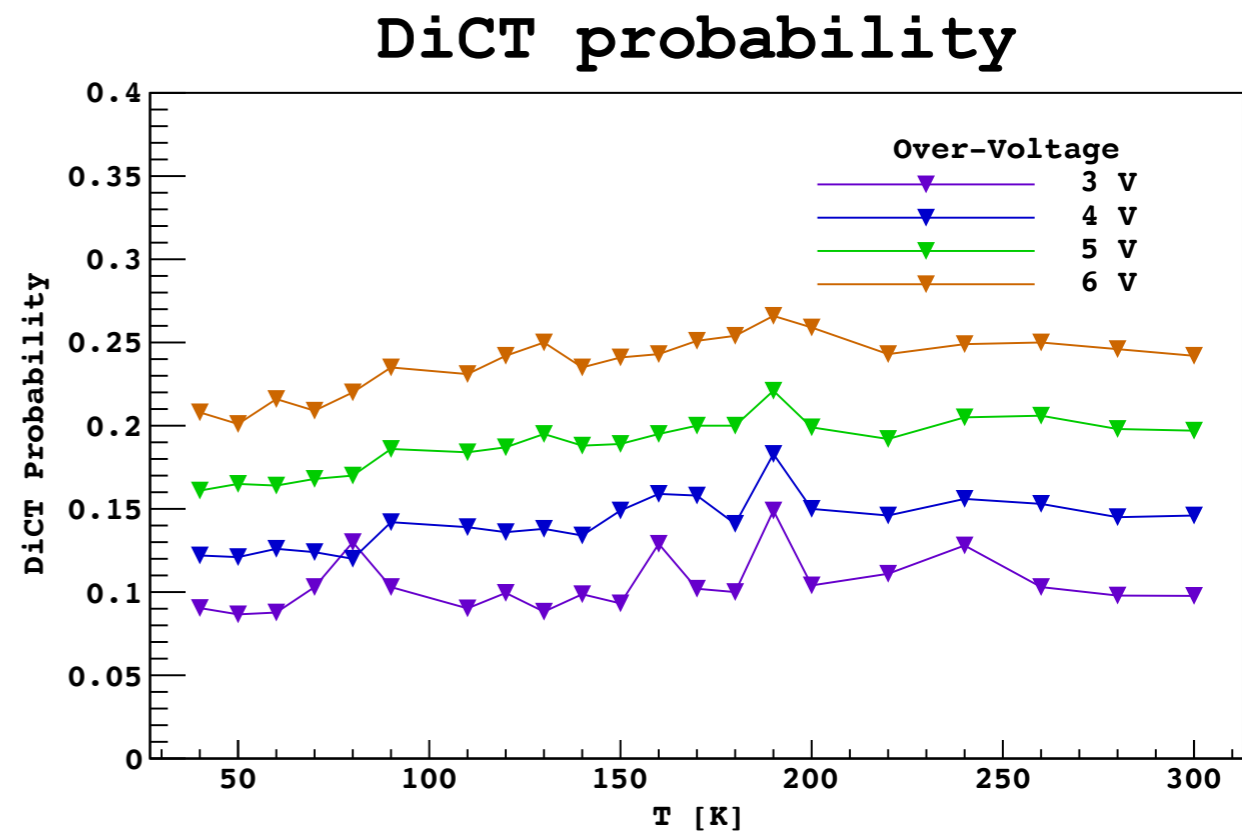
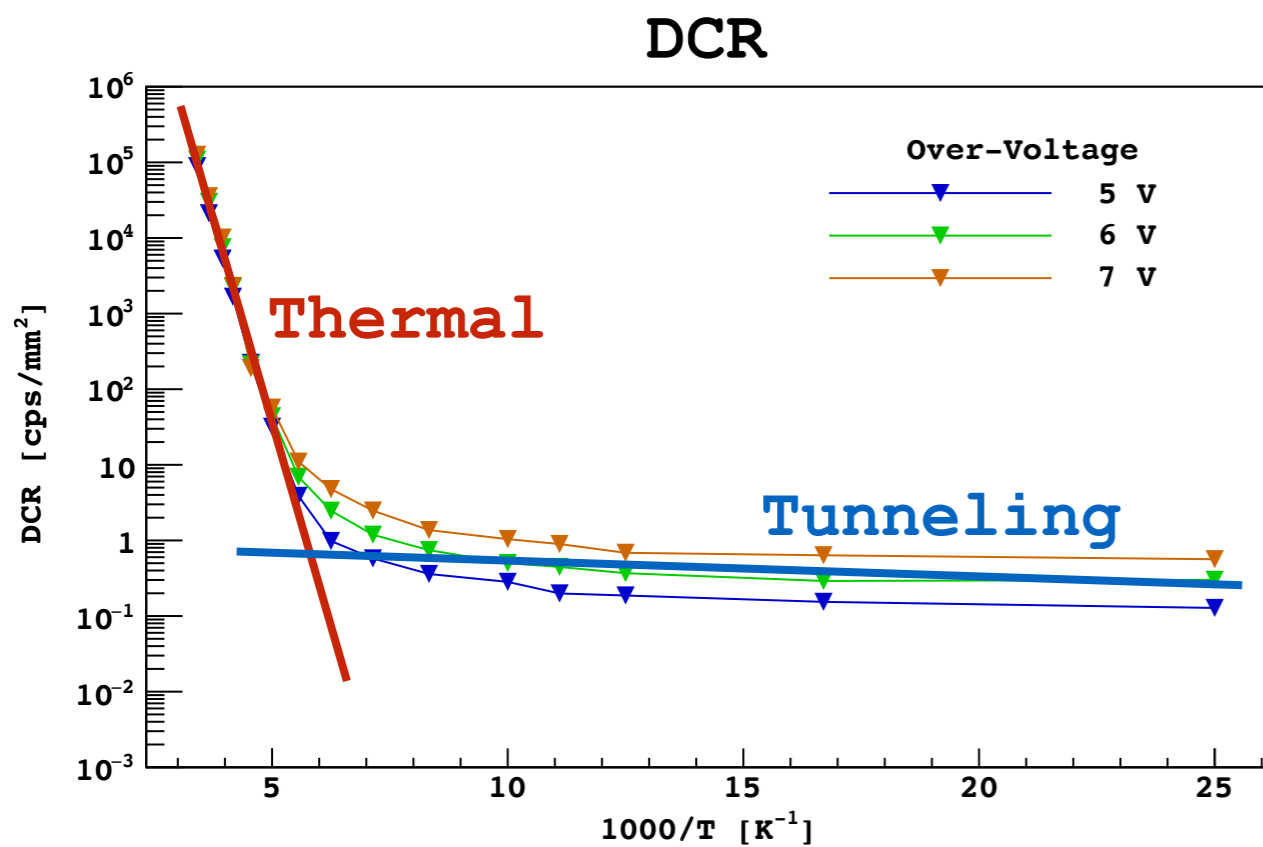


- Primary: DCR
- Correlated: DiCT, DeCT, AP
- An effective way to distinguish the several components of CN is a Amplitude vs  $\Delta t$  scatter plot.





# Noises vs Temperature



# PMT Vs SiPM

3" diameter



4x4mm<sup>2</sup>



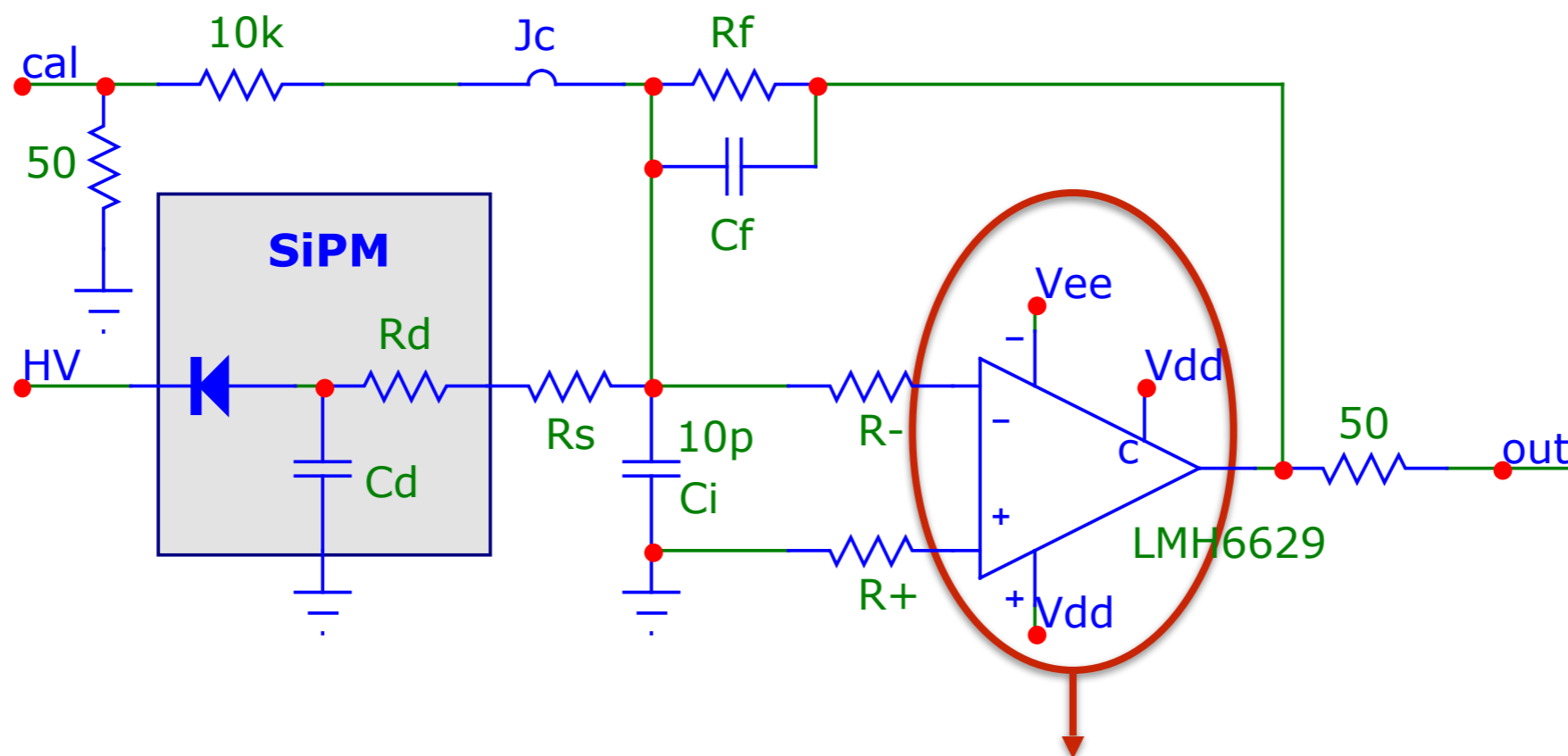
Comparison among commercial devices at CRYOGENIC temperature (87K)

	PMT	SiPM
Bias Voltage	~ (1000-2000) V	~ (30-40) V
Sensitivity to B fields	Yes	No
QE/PDE@420nm@300K	34%	(20-50) %
Packing efficiency	60%	(80-90) %
SPE resolution	20%	~ (1-5) %
Dynamic range	>> 10 <sup>3</sup>	O(10 <sup>3</sup> )
Gain	10 <sup>6</sup> -10 <sup>7</sup> nominal	O(10 <sup>6</sup> )
DCR	O(1cps/PMT)	(10-100) cps/mm <sup>2</sup>



# Electronics: a fast cryogenic pre-amp

- Pre-amplification is needed near the photo-sensor.
- SiPMs are current generators and present a huge output capacitance ( $\sim 50\text{pF}/\text{mm}^2$ ).
- A Transimpedance amplifier (TIA) is the most suitable choice: **High Bandwidth** and **Low Noise** at cryogenic temperatures.

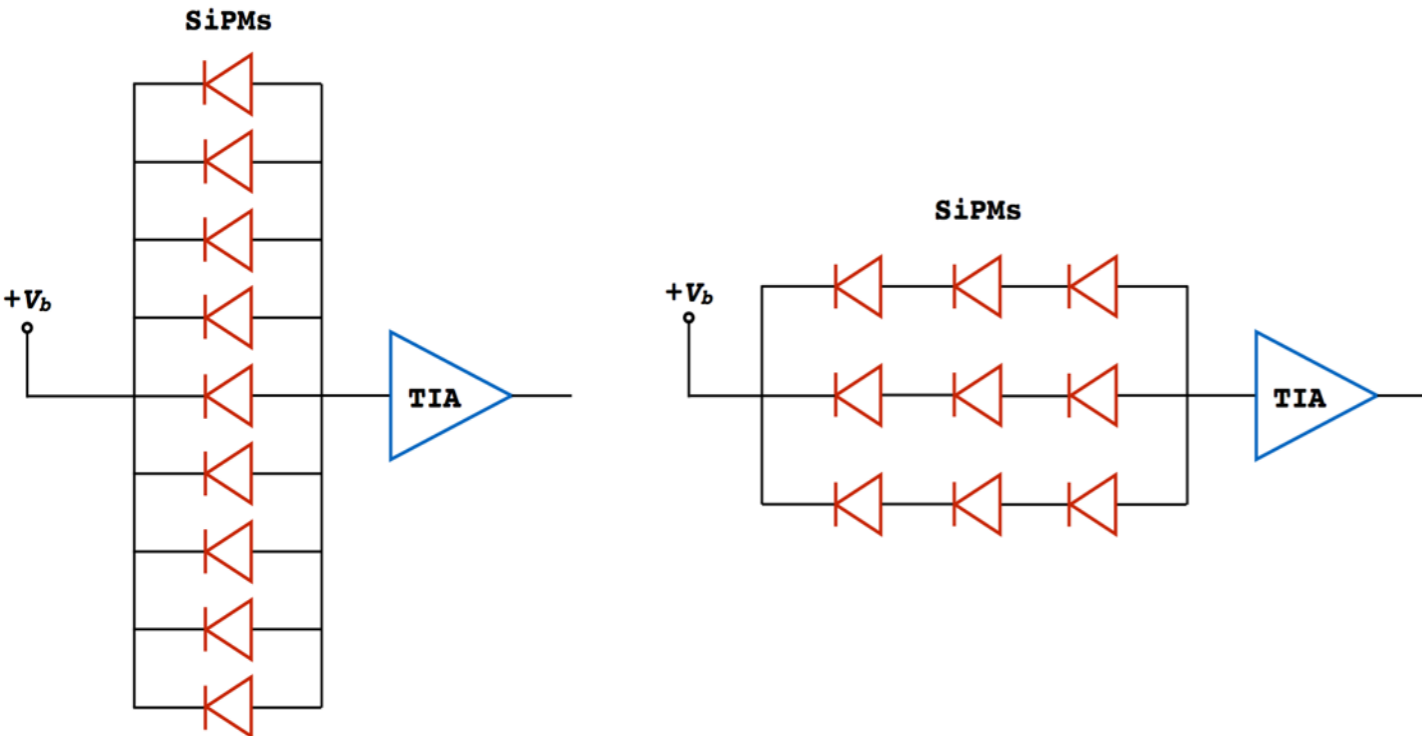


But a high BW, Low-Noise Op.Amp. is needed!  
(and should be stable at 87K)

# SiPM Tiling

Not a trivial task:

- Signal from 1 SiPM, **noise read-out from all SiPMs.**
- Huge input capacitance reduces the BW of the system.



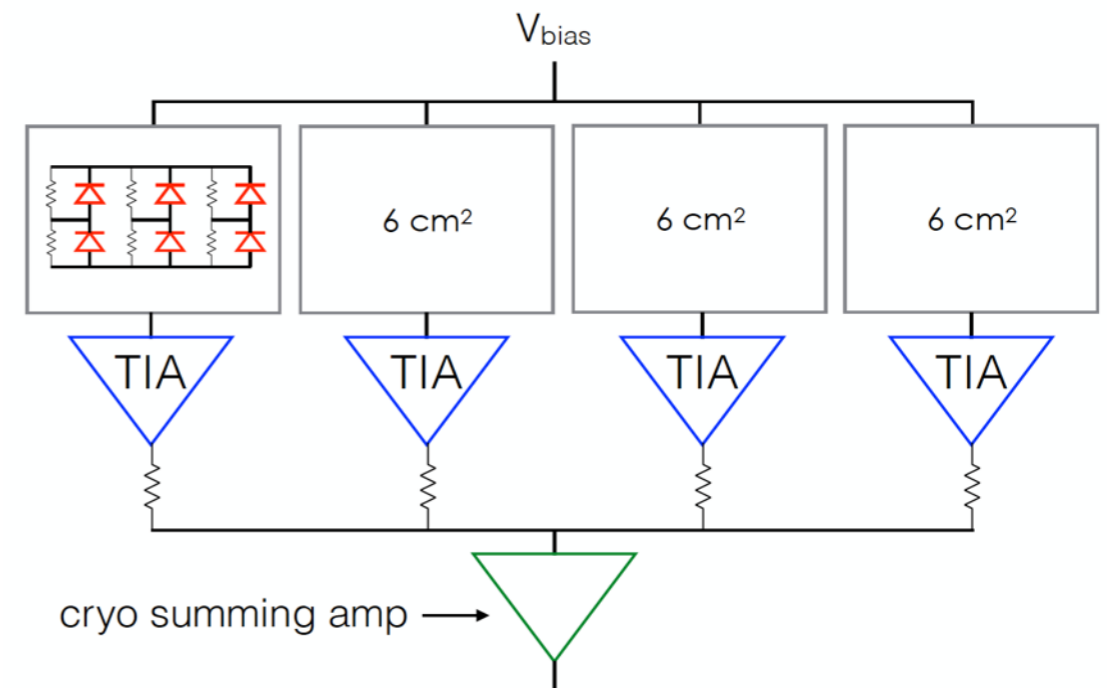
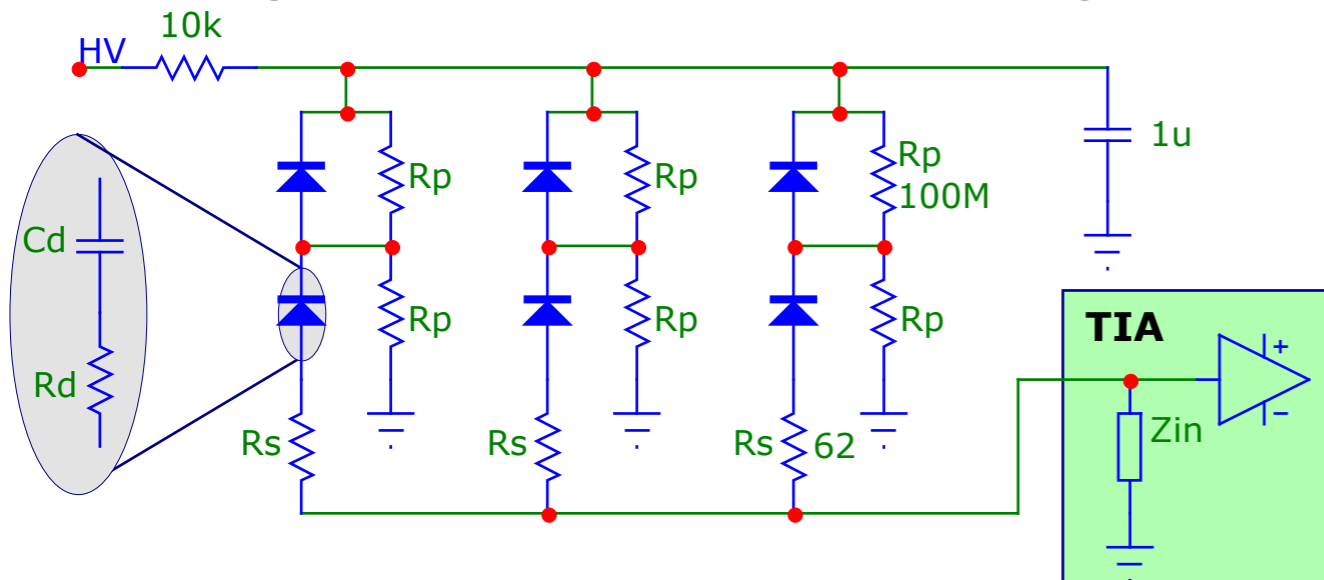
$$SNR_{9p} = \frac{S_1}{3N_1} = \frac{1}{3} SNR_1$$

$$SNR_{3s3p} = \frac{S_1/3}{N_1} = \frac{1}{3} SNR_1$$

- Total Noise  $\propto \sqrt{C_{in}}$
- Signal divided  $n_{series}$
- Same BW of 1 SiPM

Parallel Configuration

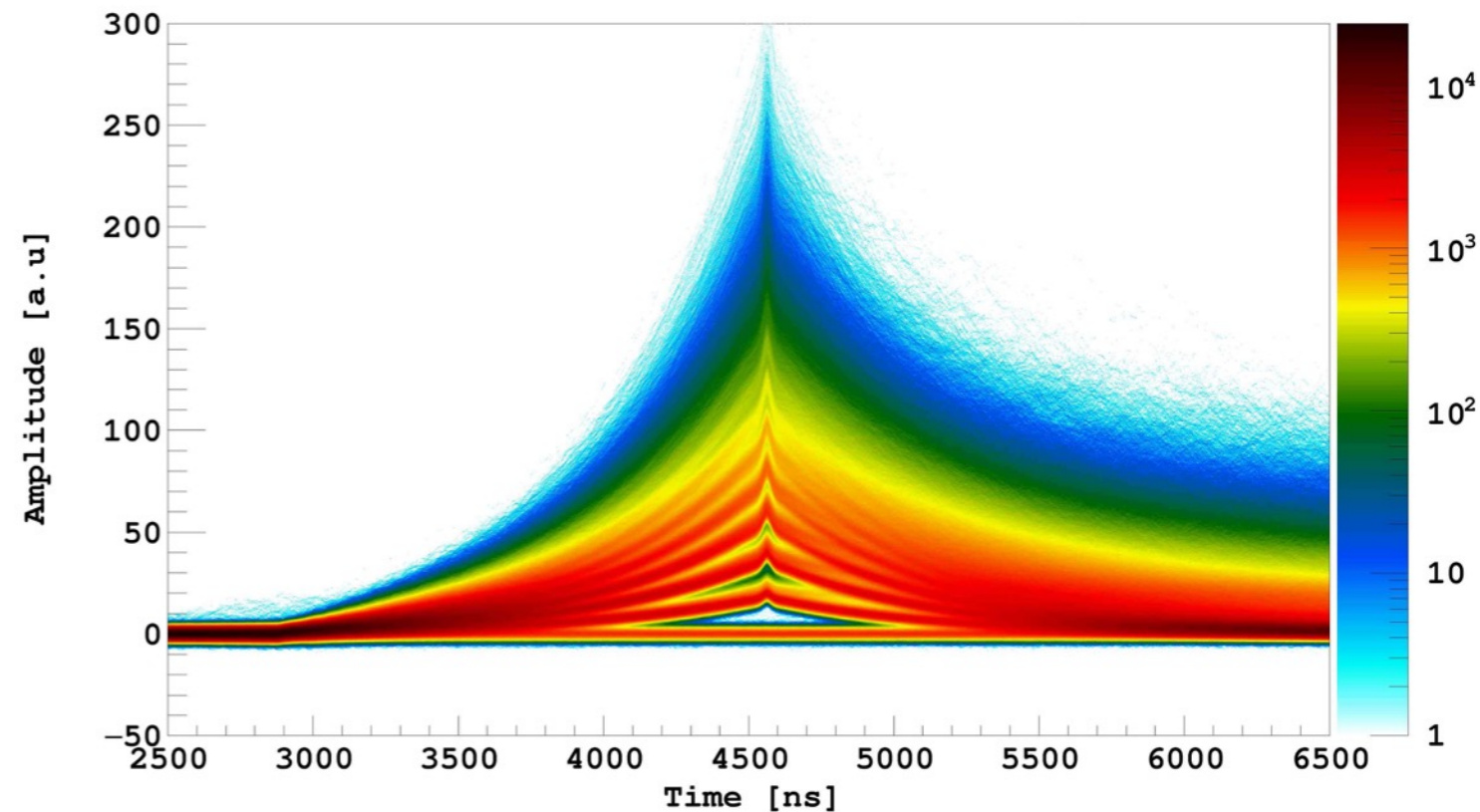
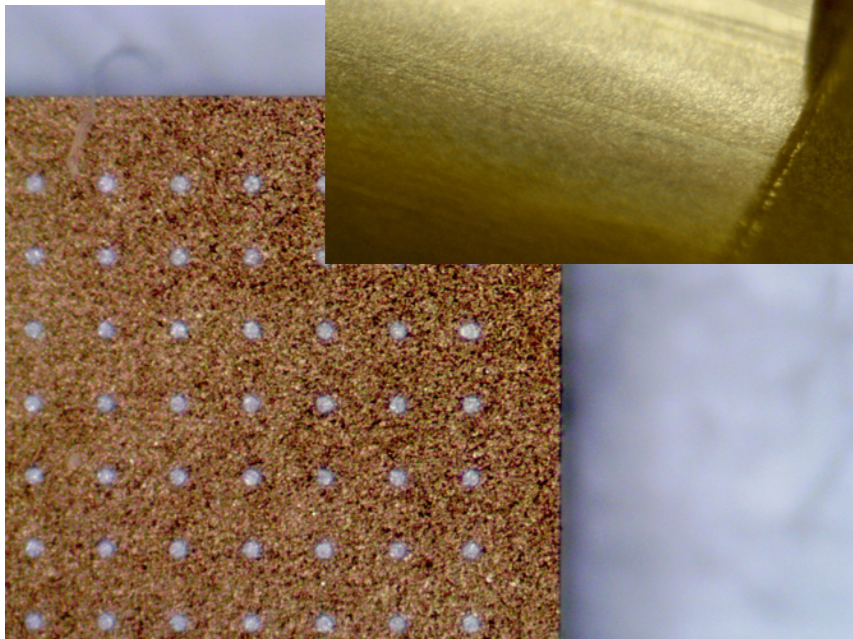
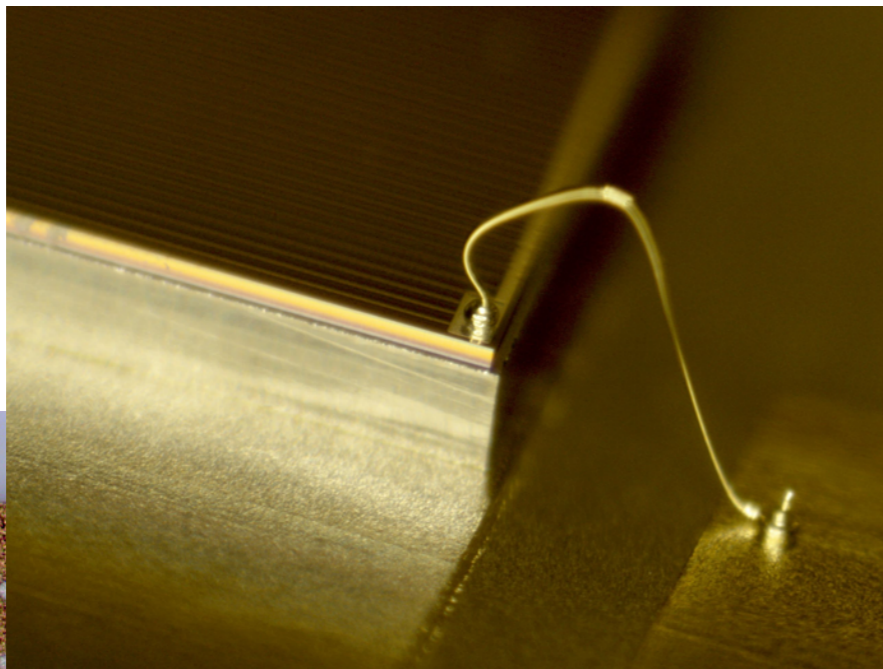
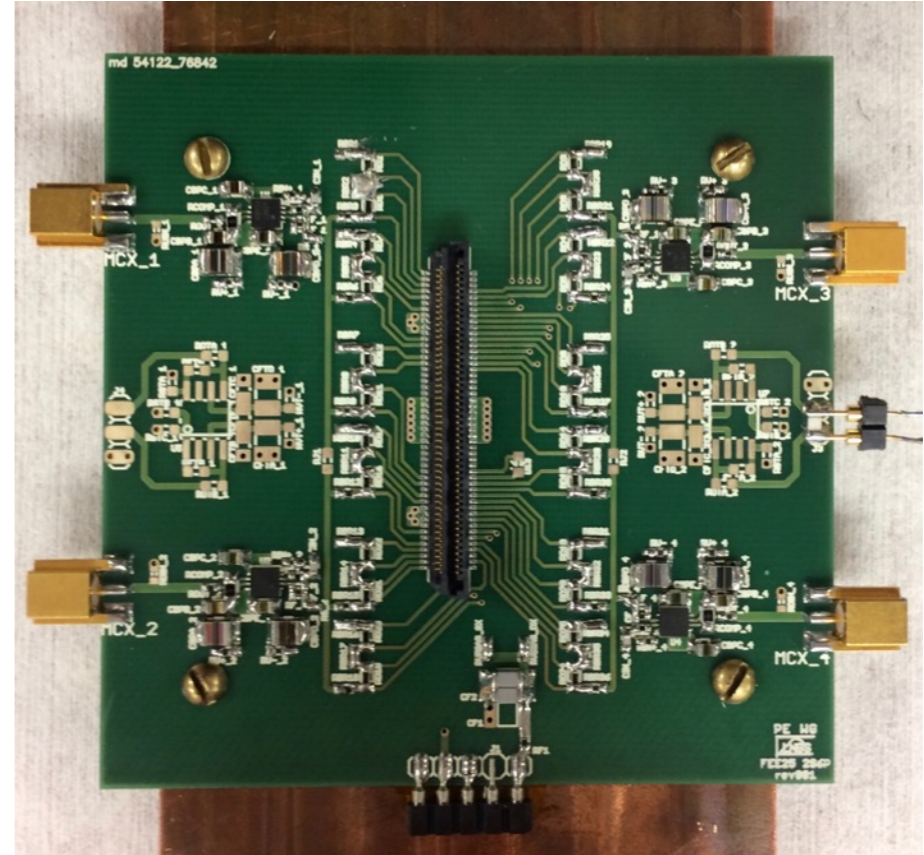
Series/Parallel Configuration





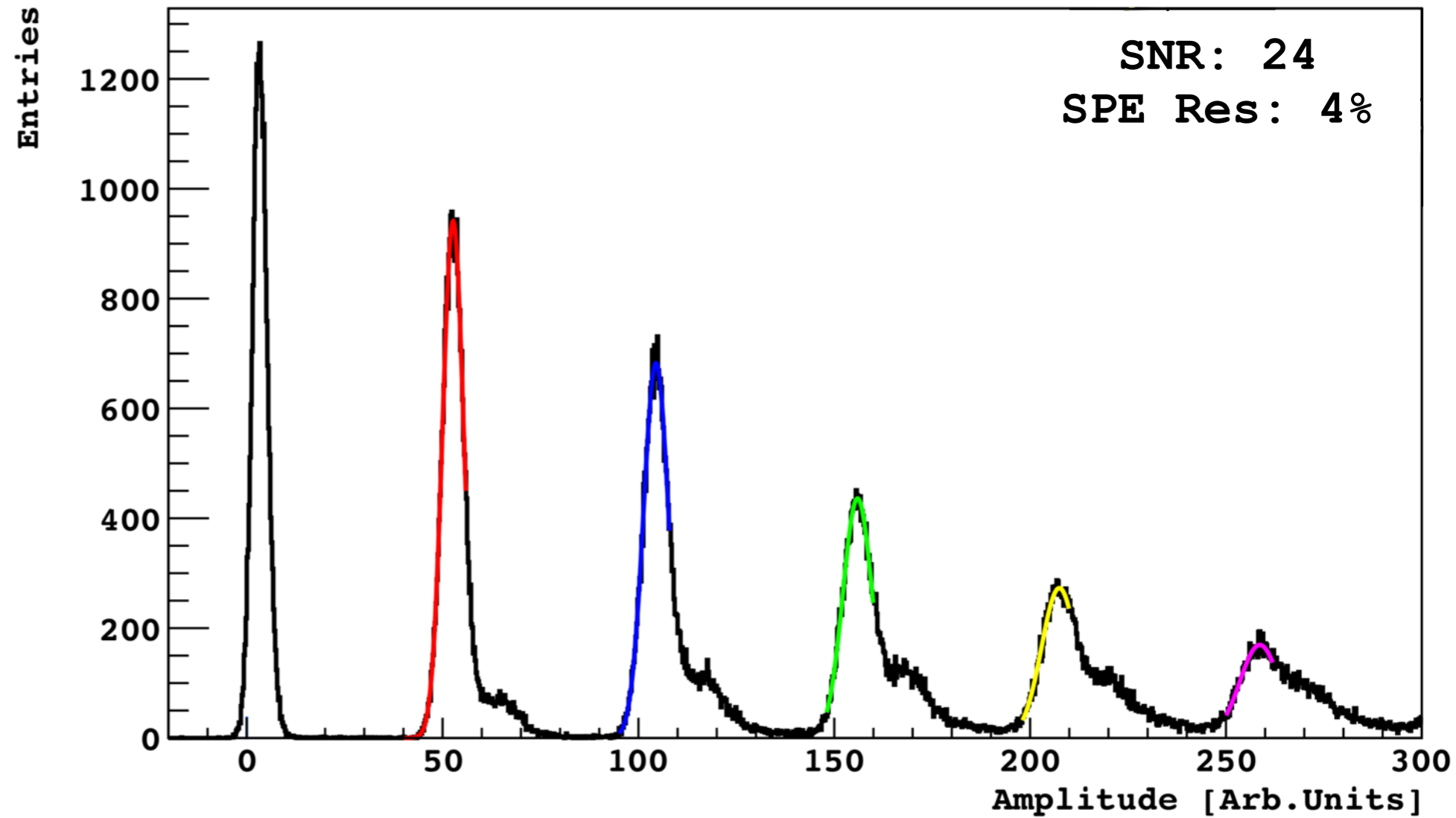
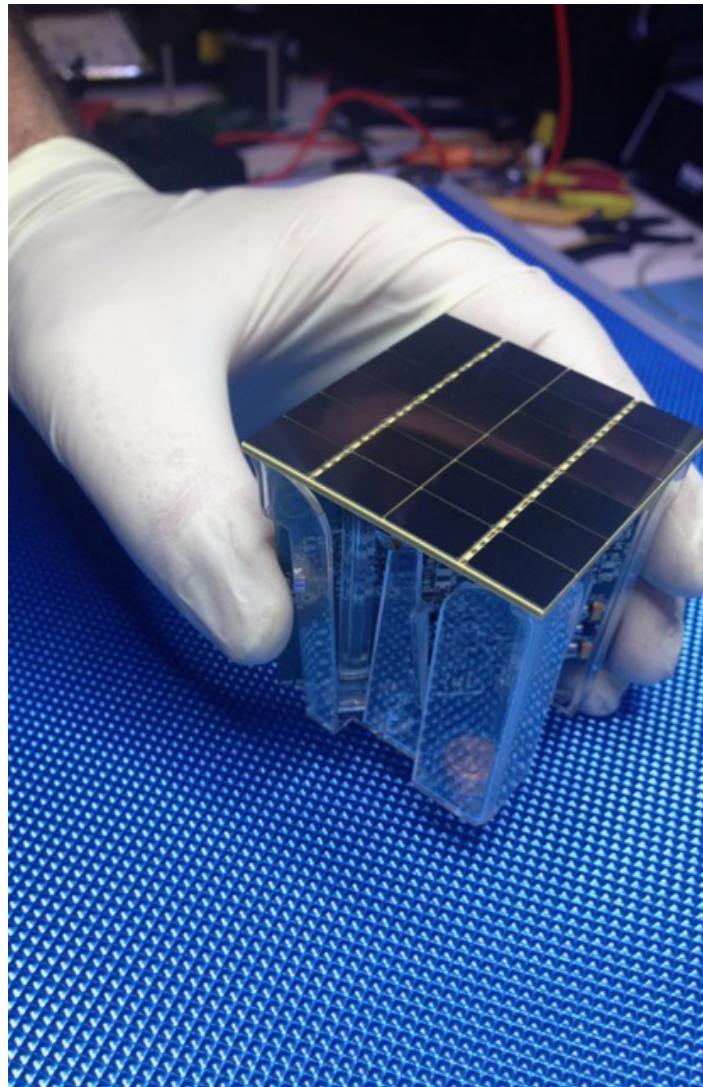
# There's no such thing as free lunch

1. Discrete electronics radiopurity
2. Packaging
3. Signal filtering

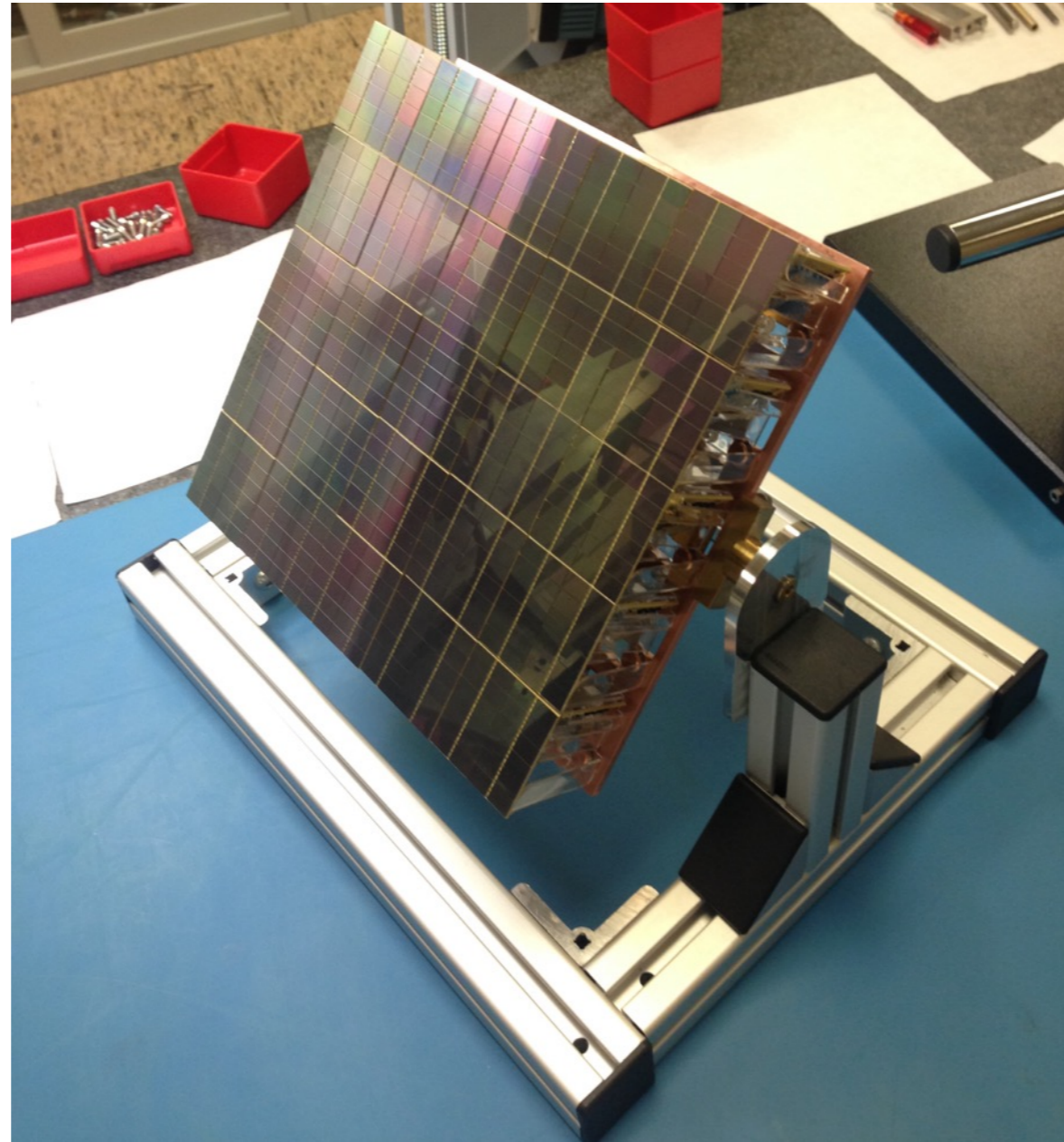




# Prototype Tile performances

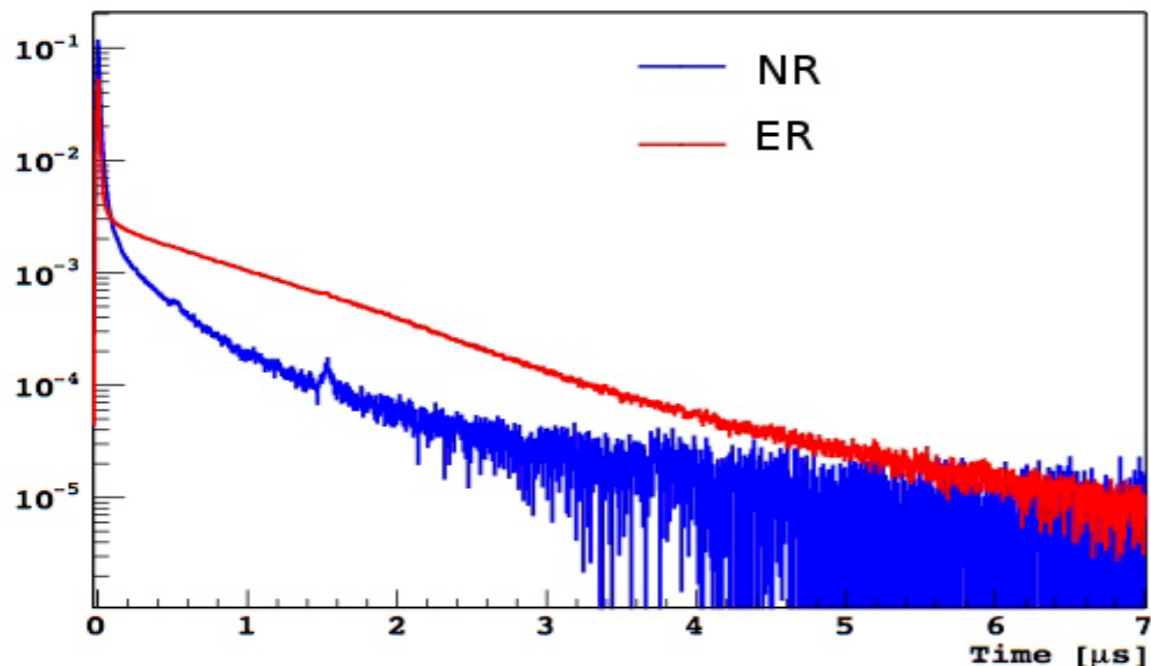






**Thank you  
for the attention!**

# ER/NR identification via PSD

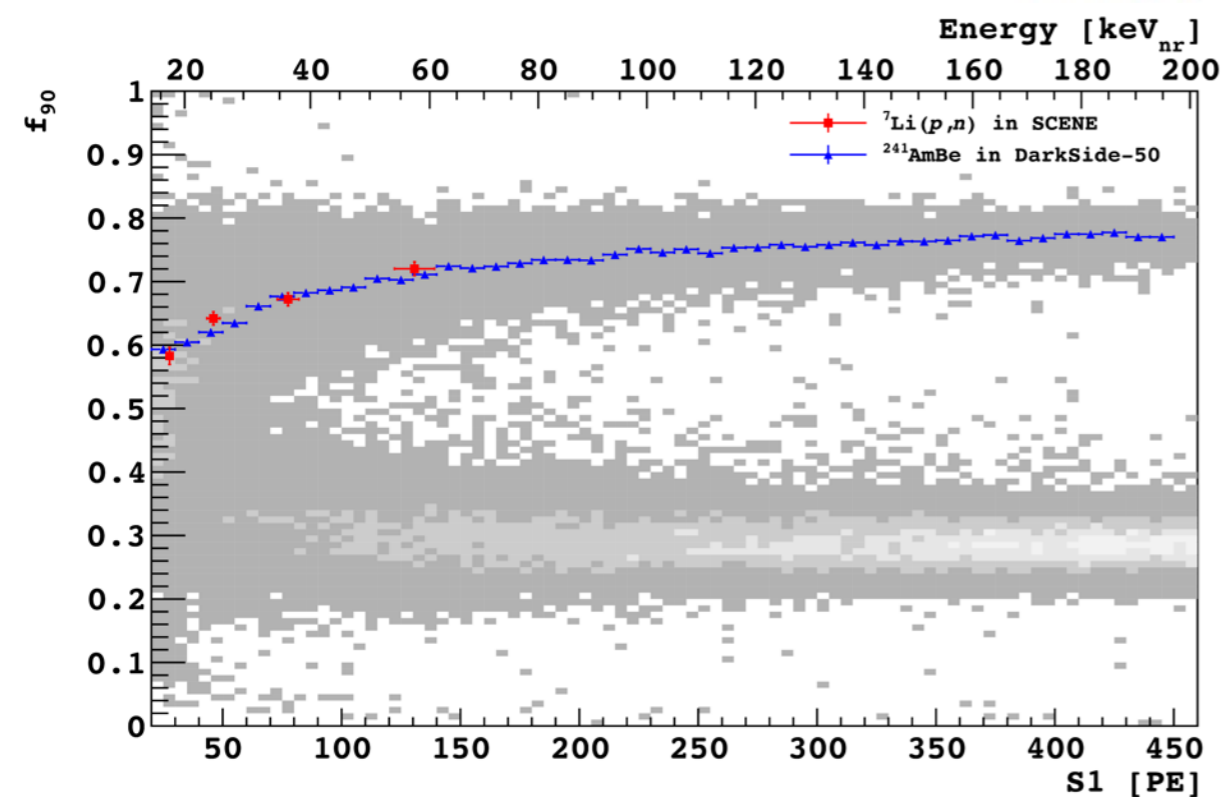


LAr scintillation light has 2 decay times:  $\tau_{fast}=7\text{ns}$ ,  $\tau_{slow}=1600\text{ns}$

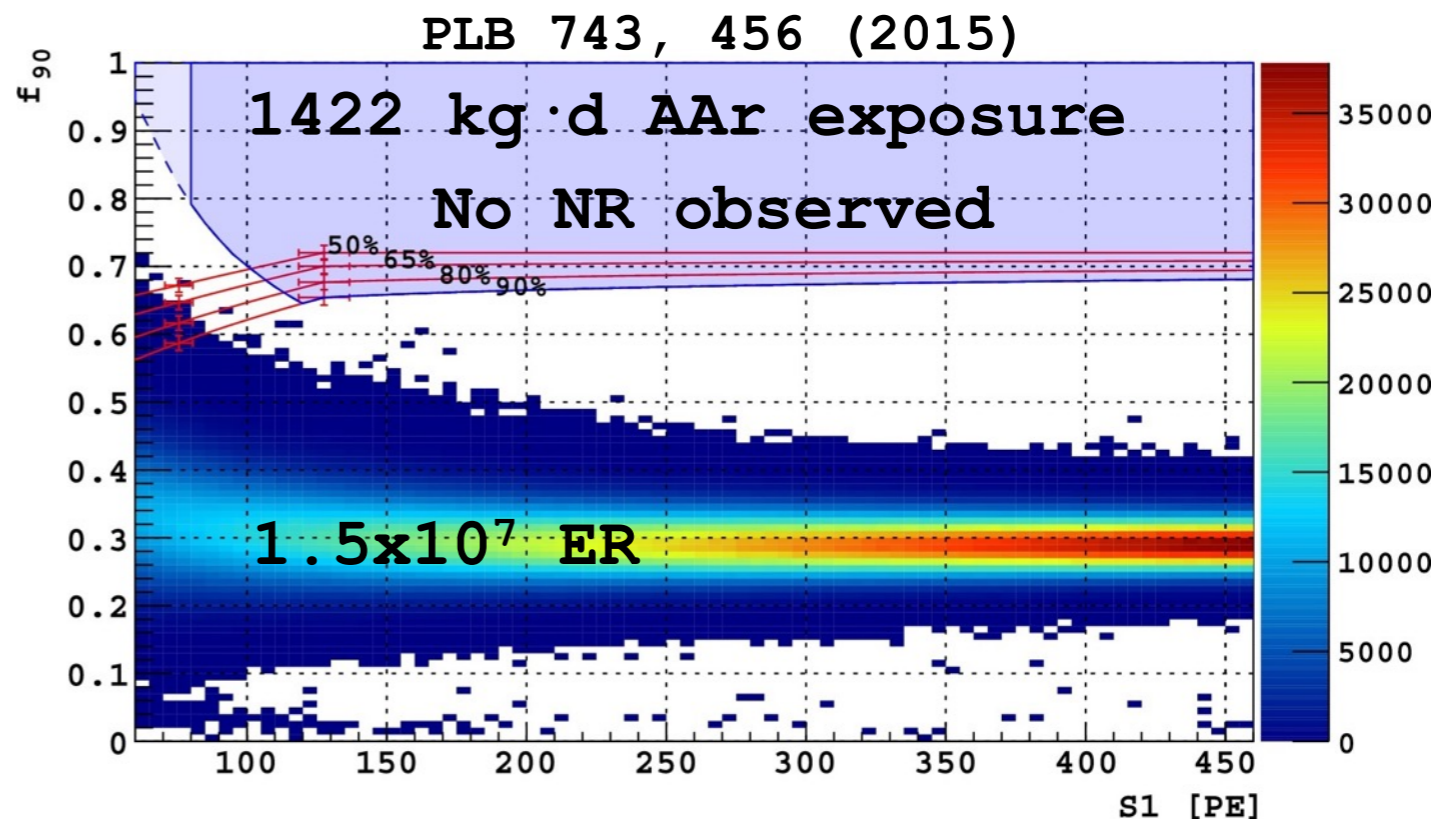
Discriminating variable:

$$f_{\text{prompt}} = \frac{\# \text{ prompt photons}}{\# \text{ total photons}}$$

In DS-50 90ns is the optimal time window to optimize PSD.



ER and NR produce light with different  $\tau_{fast}/\tau_{slow}$  fractions.

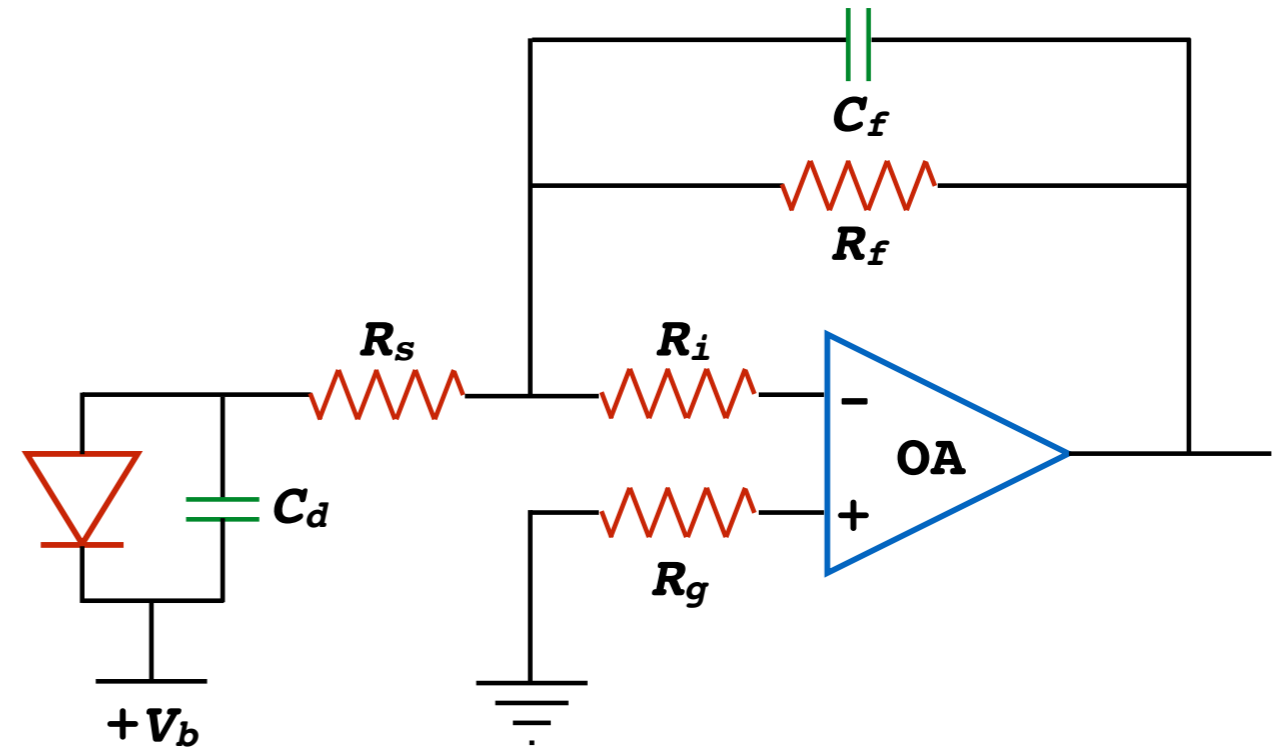


Discrimination Power  $> 1.5 \times 10^7$   
Background-free UAr exposure: 5.5ton·yr



# TIA working principle

- A TIA transforms current pulses in voltage pulses.
- Amplification is achieved "shaping" the open loop gain of the OA through a feedback on the inverting pin.
- Noise at the output of the system has 3 sources:



$$V_n^2(f) = e_n^2 |NG(f)|^2 + \left( i_n^2 + \frac{4k_b T}{R_f} \right) |T_Z(f)|^2$$

Noise Gain  $\uparrow$   
 Voltage input noise density  $\swarrow$   
 Current input noise density  $\searrow$   
 Johnson-Nyquist noise  $\swarrow$   
 Transfer function  $\uparrow$

